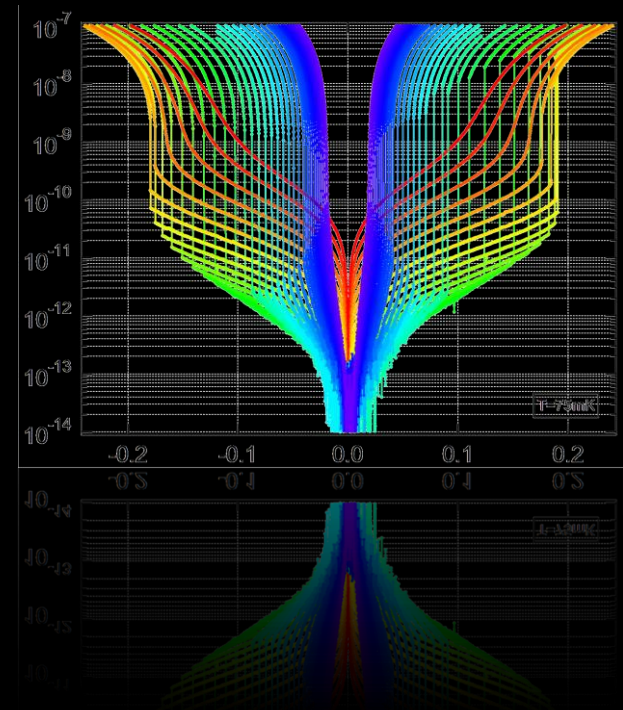


The magnetic field induced insulating state in amorphous superconductors

Benjamin Sacépé

Néel Institute, CNRS & Univ. Grenoble Alpes



Strongly disordered and inhomogeneous superconductivity

Grenoble, Nov. 2016



Idan Tamir



Maoz Ovadia
(Harvard)



Dan Shahar



Johanna Seidemann



Benjamin Piot



Christoph Strunk

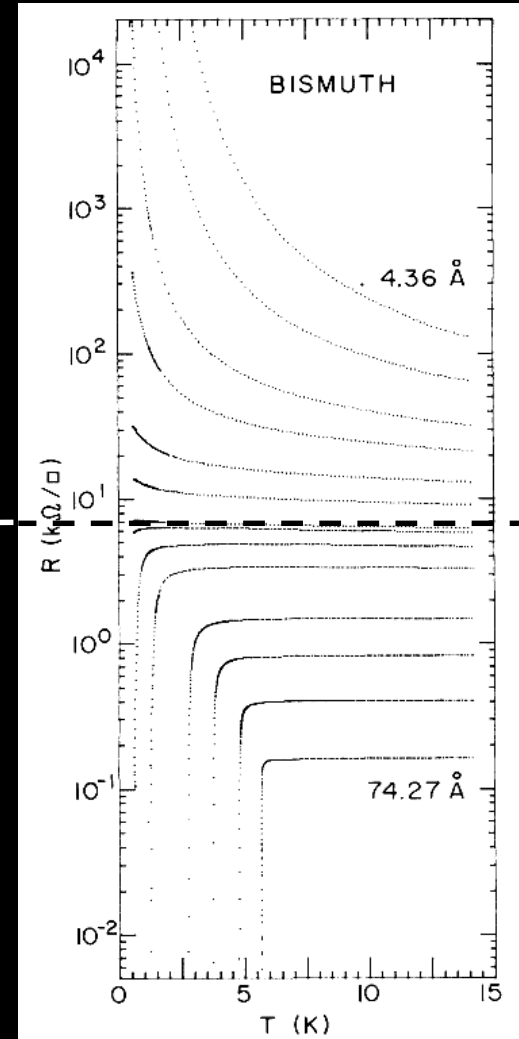


The Superconductor-Insulator Transition

Strongin et al.
Phys. Rev. B 1, 1078 (1970)

Haviland, Lui, and Goldman,
Phys. Rev. Lett. 62, 2180 (1989)...

Reviews: Finkel'stein ('94)
Markovic and Goldman ('98)
Gantmakher and Dolgoplov ('10)



Thickness

Prototypical quantum phase transition

Strictly $T=0$.

Driven by:

Thickness

Magnetic field

Disorder

Carrier density

Pressure

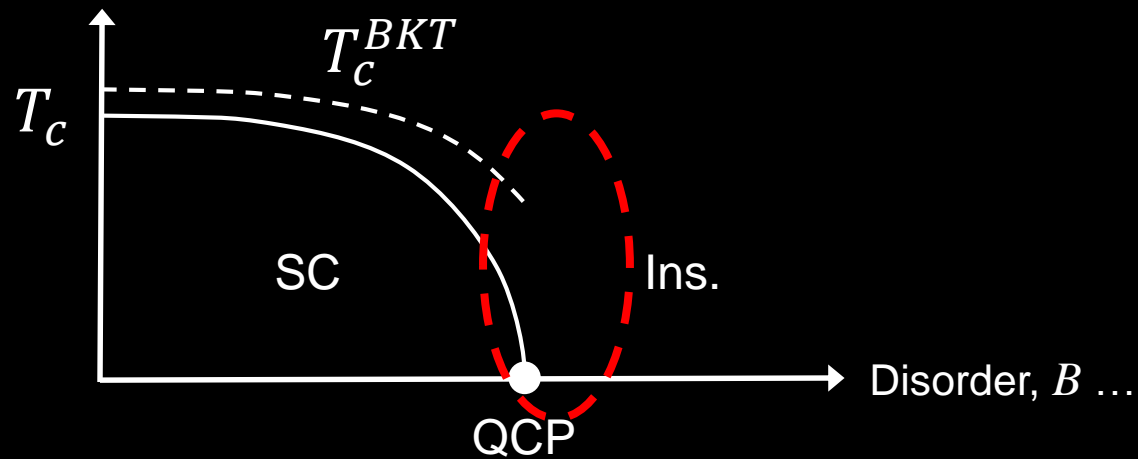
Chemical composition

Structural composition

...

Suppression of superconductivity

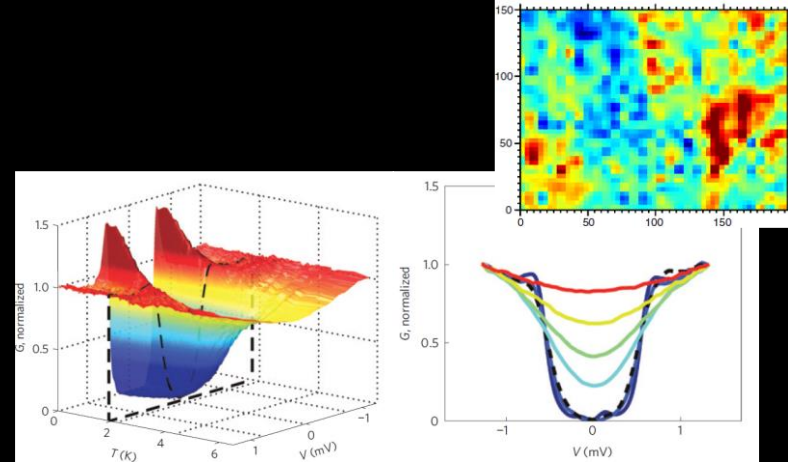
M.P.A. Fisher ('90)



Insulator with localized Cooper-pairs ?

Localization of preformed Cooper pairs in disordered superconductors

Benjamin Sacépé^{1,2,*†‡}, Thomas Dubouchet^{1†}, Claude Chapelier¹, Marc Sanquer¹, Maoz Ovadia², Dan Shahar², Mikhail Feigel'man³ and Lev Ioffe⁴



Annals of Physics 325 (2010) 1390–1478

Contents lists available at ScienceDirect



Annals of Physics

journal homepage: www.elsevier.com/locate/aop

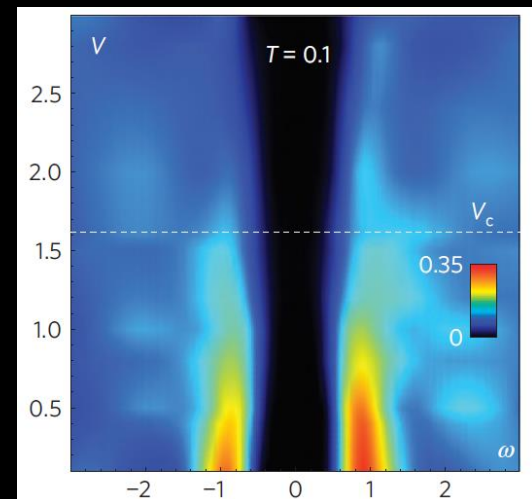
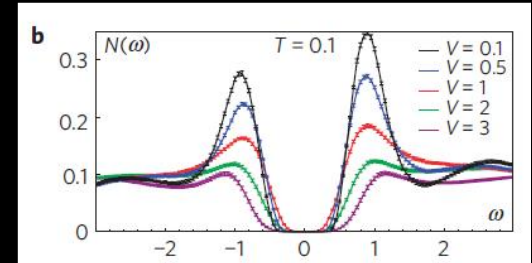


Fractal superconductivity near localization threshold

M.V. Feigel'man^{a,b}, L.B. Ioffe^{a,c,d,*}, V.E. Kravtsov^{a,e}, E. Cuevas^f

Single- and two-particle energy gaps across the disorder-driven superconductor-insulator transition

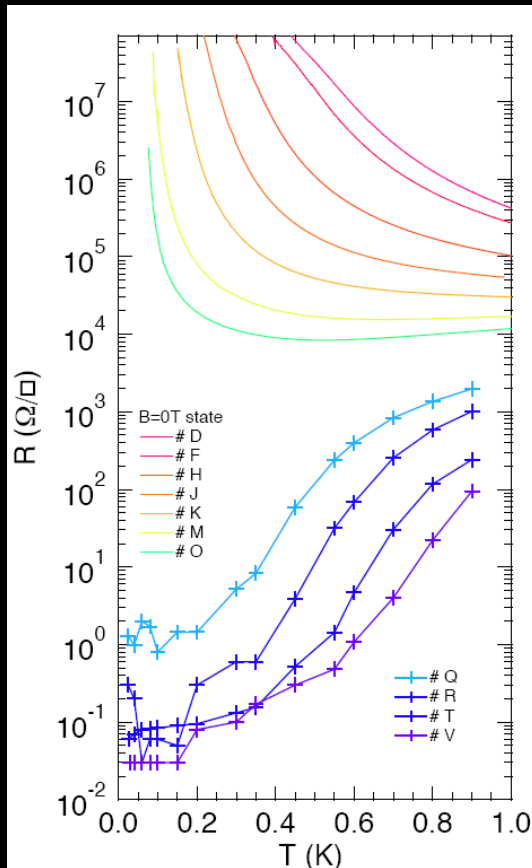
Karim Bouadim, Yen Lee Loh, Mohit Randeria and Nandini Trivedi*



Direct superconductor-insulator transition

Amorphous indium oxide films

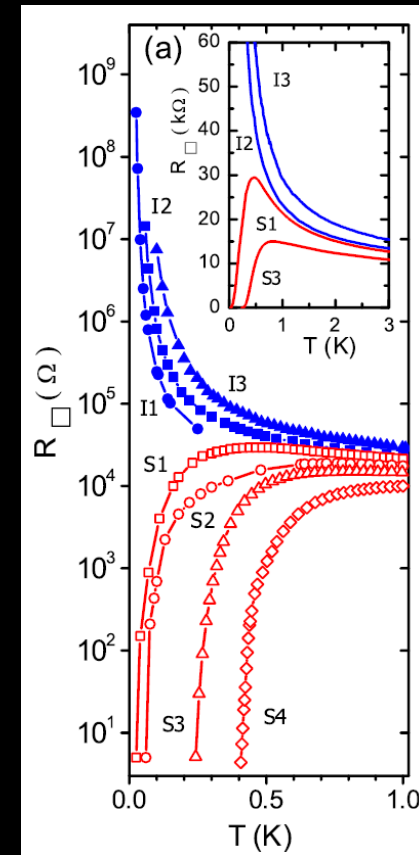
D. Shahar's group



$$n \lesssim 10^{21} \text{ cm}^{-3}$$

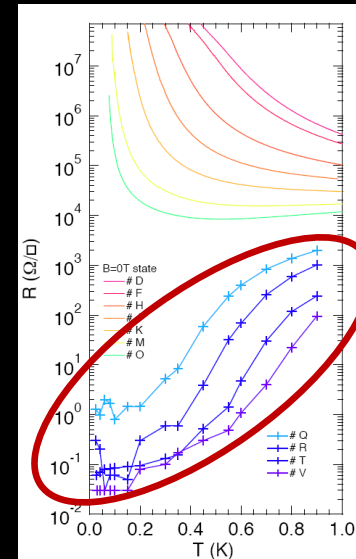
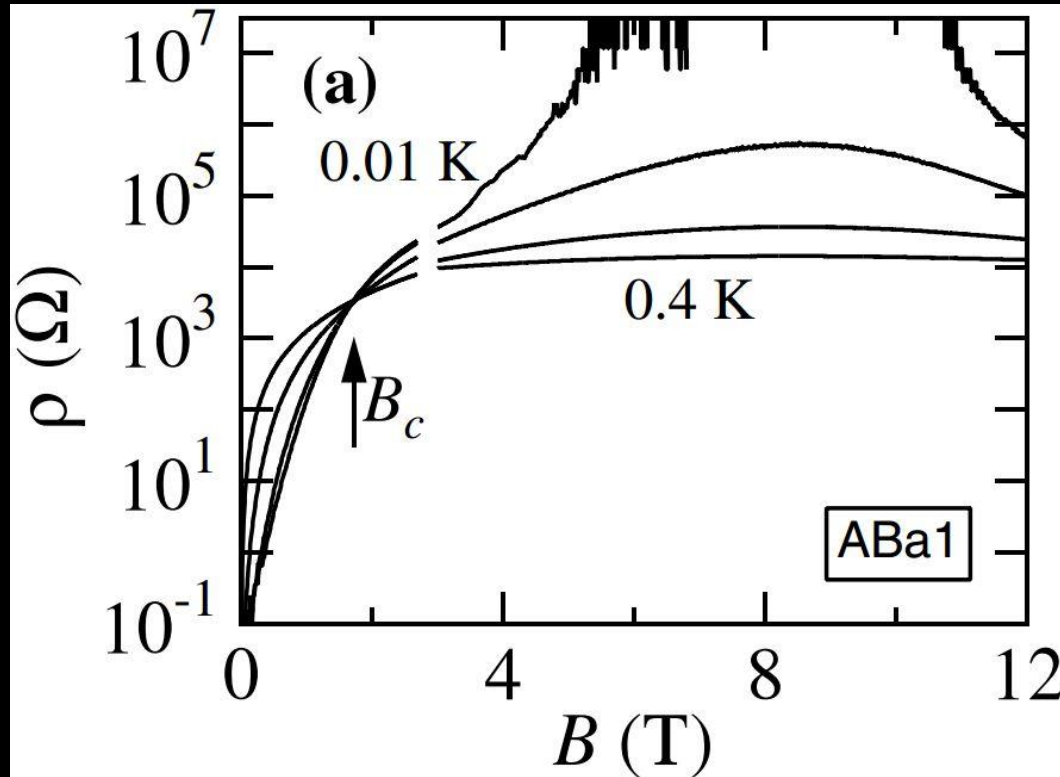
Titanium nitride

T. Baturina PRLs ('07)



$$n \lesssim 10^{22} \text{ cm}^{-3}$$

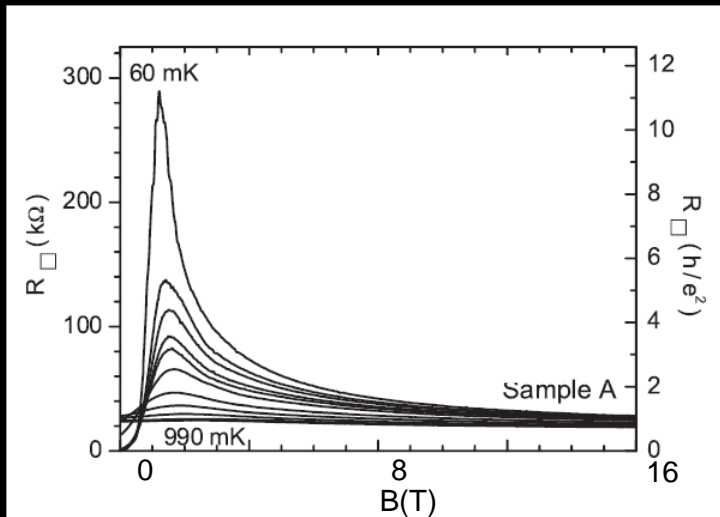
Giant magnetoresistance peak



Sambandamurthy et. al. *PRL* ('05)

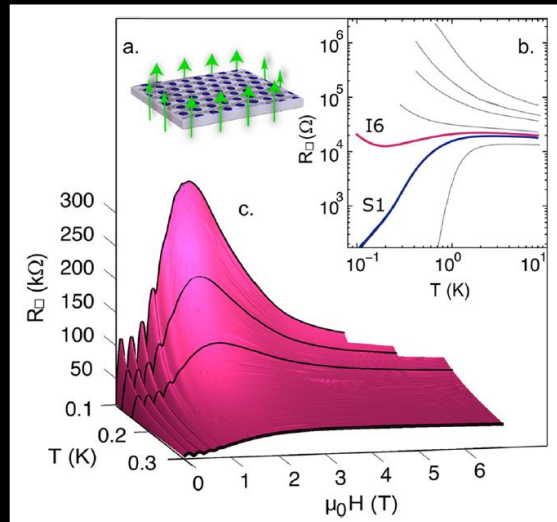
Giant magnetoresistance peaks

Titanium nitride



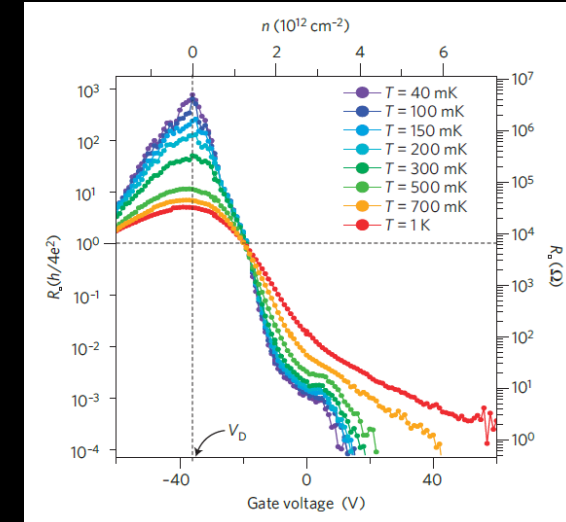
Baturina et al. *PRLs* ('07)

Quenched Bi



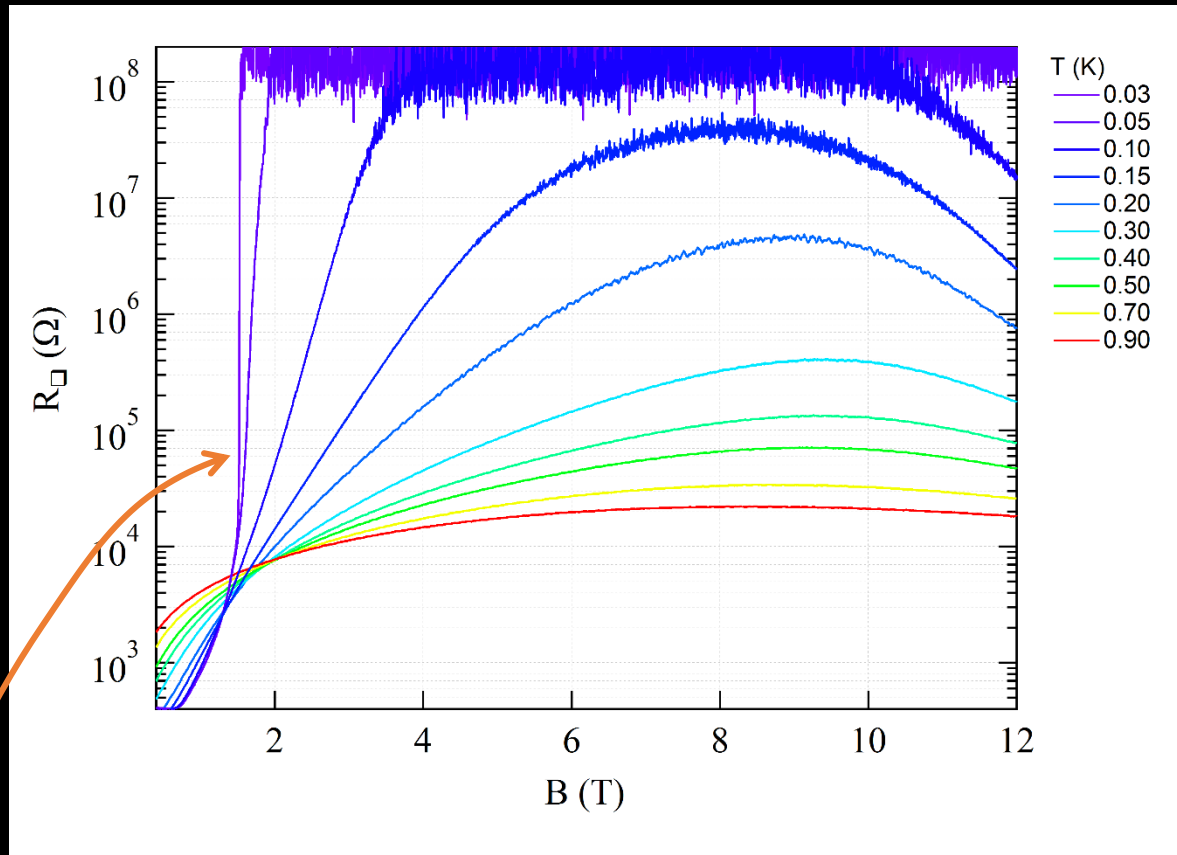
J. Valles group, *Science* ('07), *PRL* ('09)

Tin decorated insulating graphene



Allain et al. *Nature Mat.* ('12)

Insulating peak in a:InO



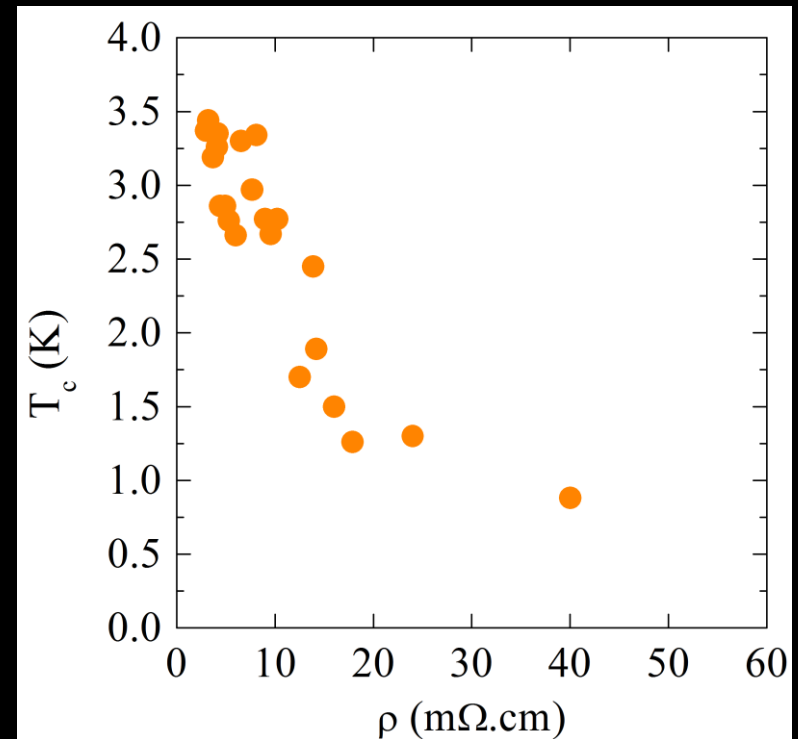
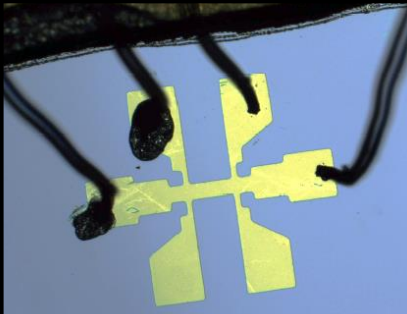
R raises by 1 decade per 0.01 tesla

Paalanen, Hebard, Ruel PRL ('90)
Sambandamurthy et al. PRL ('04)
Steiner, Kapitulnik et al. PRL ('05)

Disorder-dependence of the insulating peak

Amorphous indium oxide (a:InO)

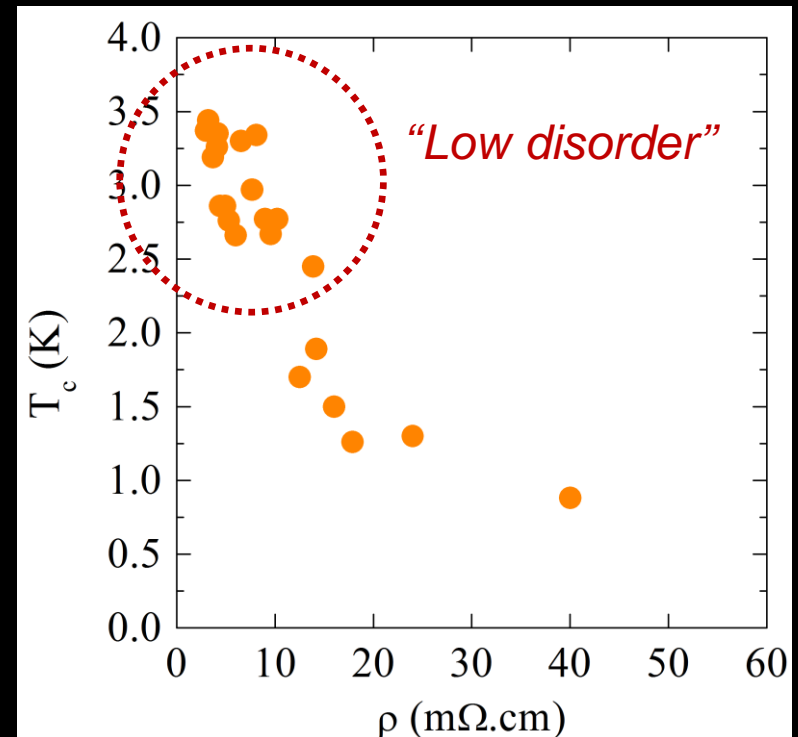
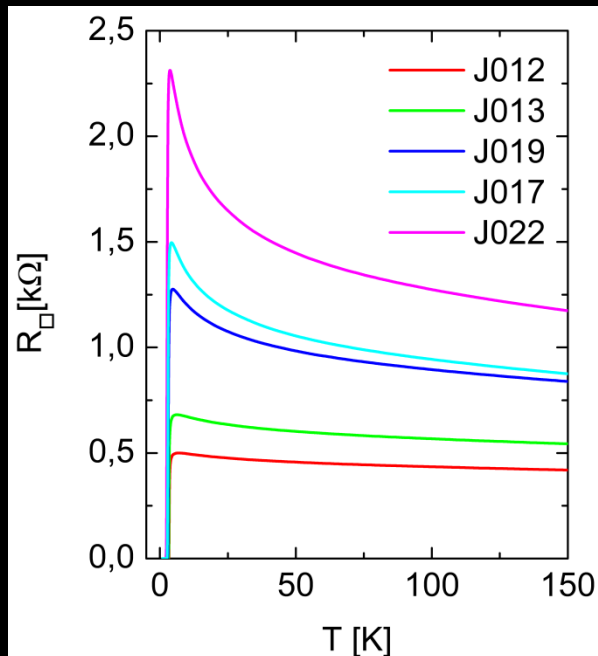
- E-gun evaporation of In_2O_3 on SiO_2 under O_2 pressure
- 30-60 nm thick
- e-density : $n \sim 10^{20} - 10^{21} \text{ cm}^{-3}$
- Disorder : $k_F l_e \sim 0.3 - 0.4$



Disorder tuned by annealing, thickness or O_2 pressure

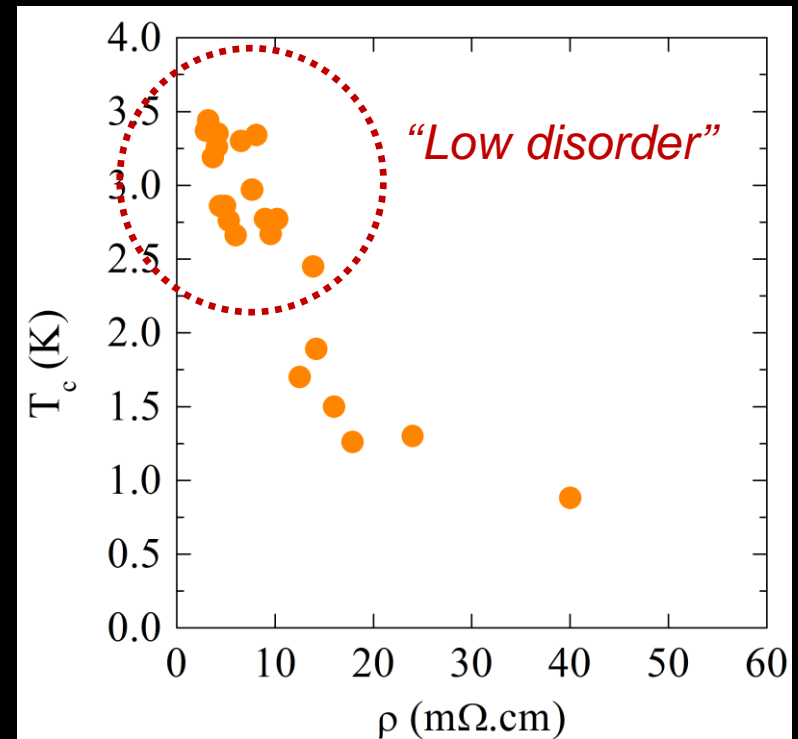
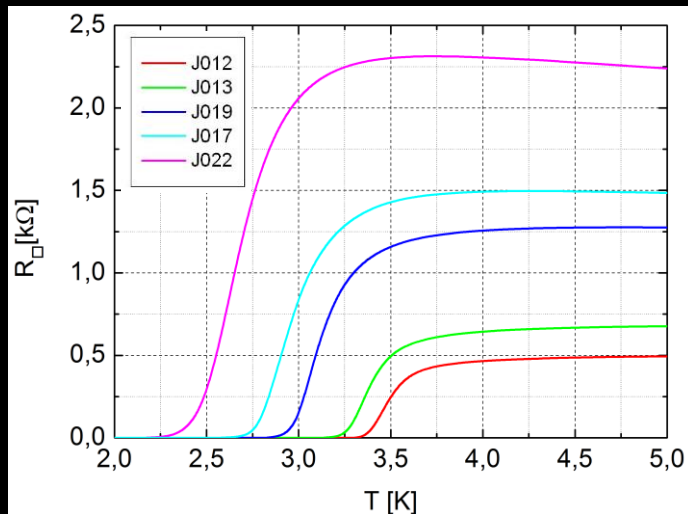
Amorphous indium oxide (a:InO)

- E-gun evaporation of In_2O_3 on SiO_2 under O_2 pressure
- 30-60 nm thick
- e-density : $n \sim 10^{20} - 10^{21} \text{ cm}^{-3}$
- Disorder : $k_F l_e \sim 0.3 - 0.4$

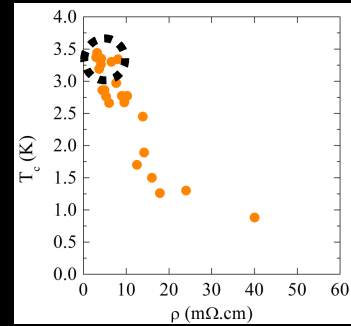
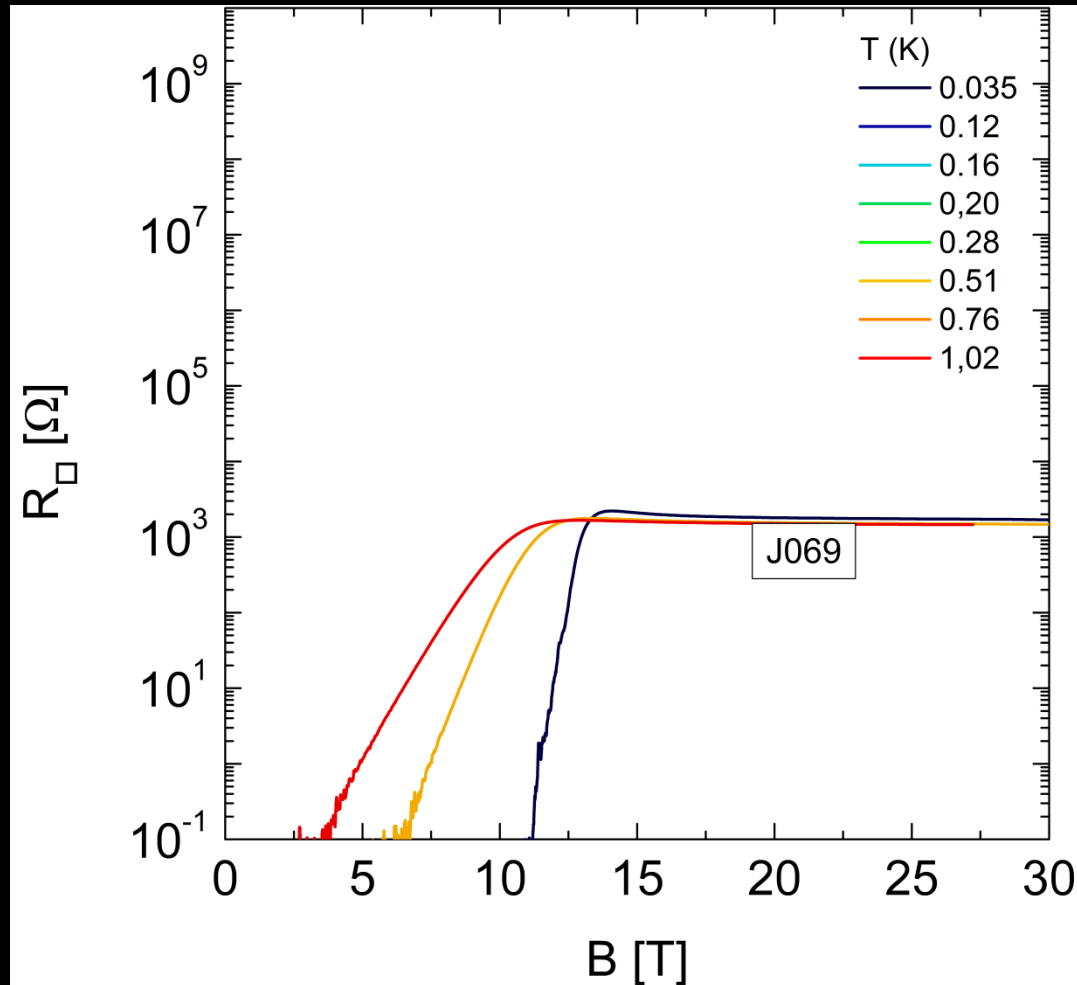


Amorphous indium oxide (a:InO)

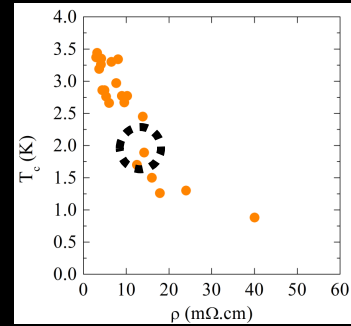
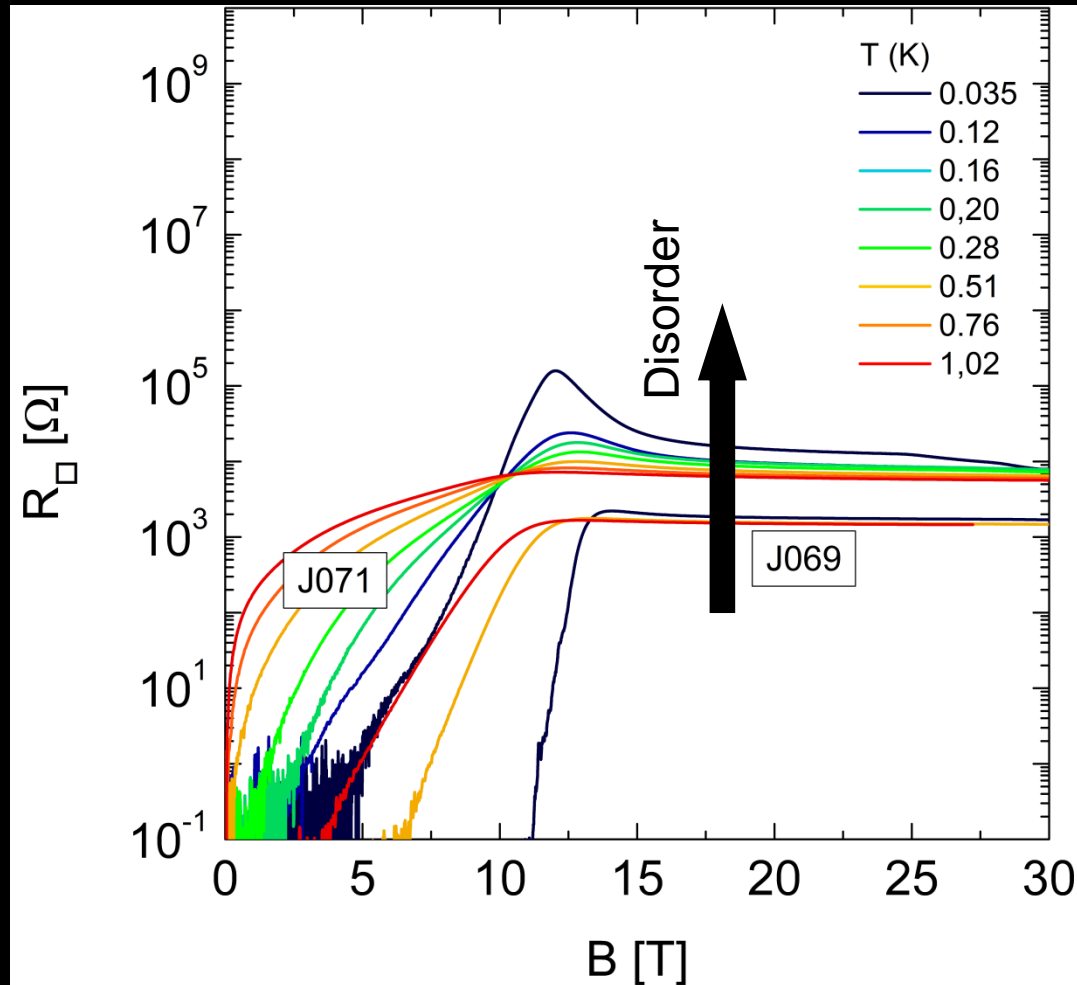
- E-gun evaporation of In_2O_3 on SiO_2 under O_2 pressure
- 30-60 nm thick
- e-density : $n \sim 10^{20} - 10^{21} \text{ cm}^{-3}$
- Disorder : $k_F l_e \sim 0.3 - 0.4$



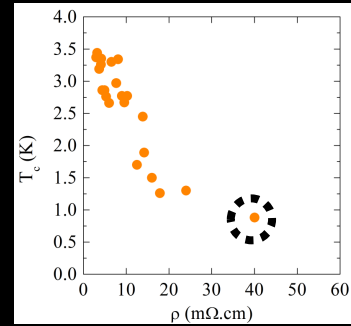
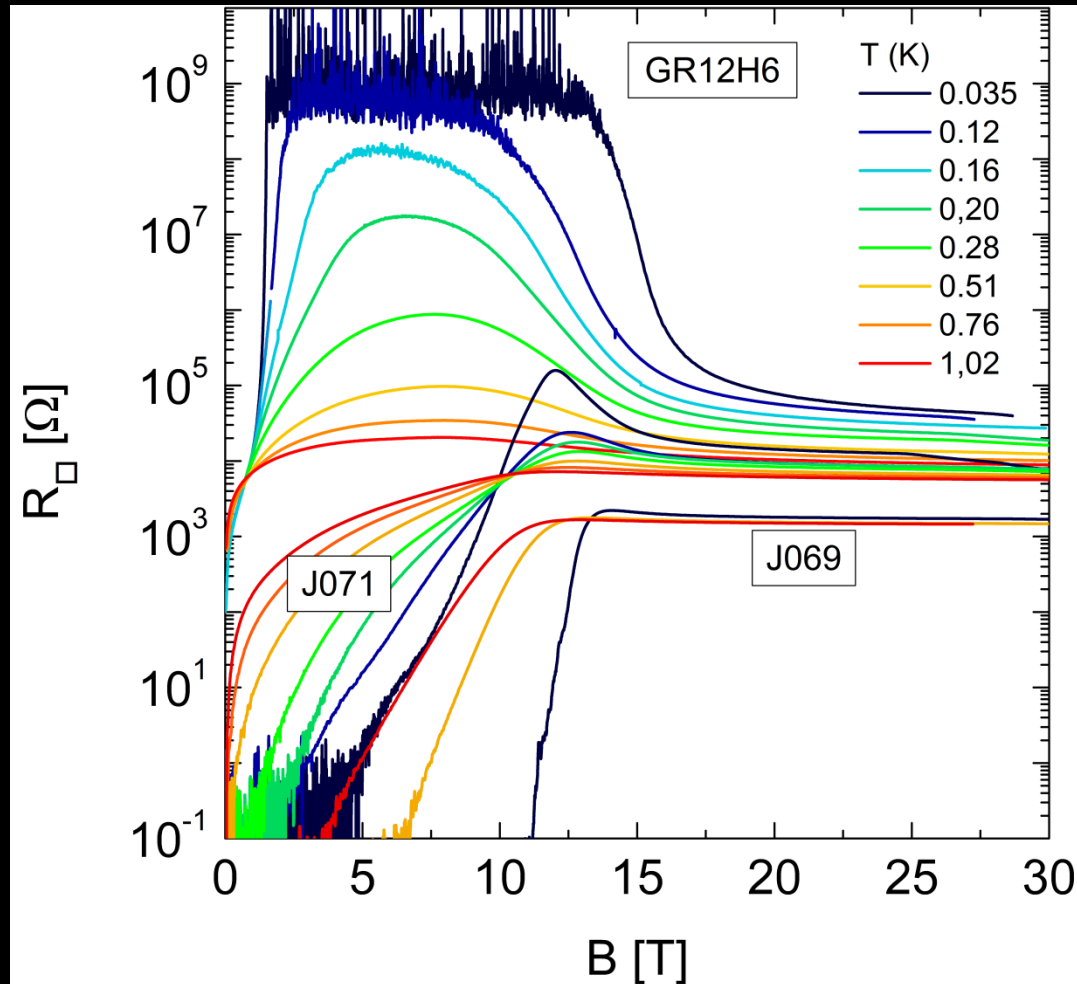
Low disorder



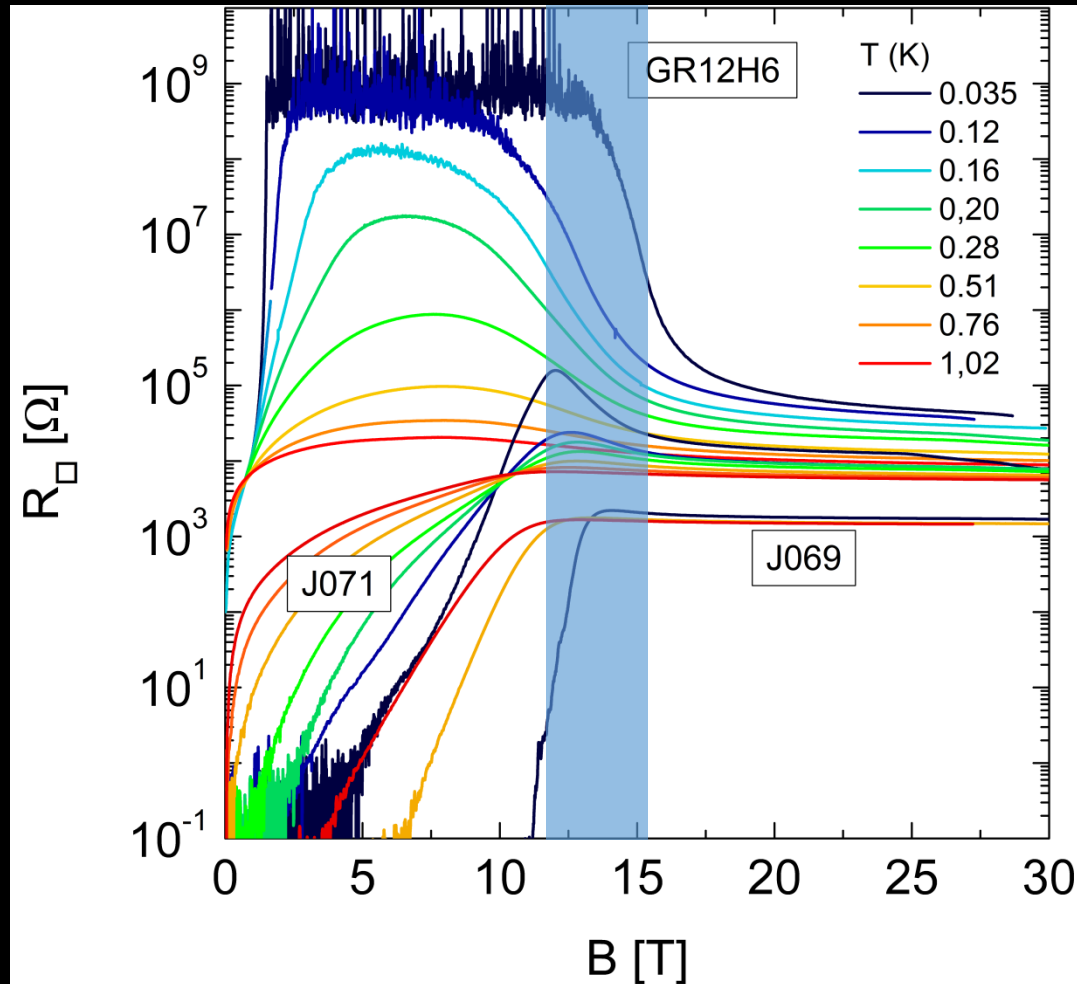
Medium disorder



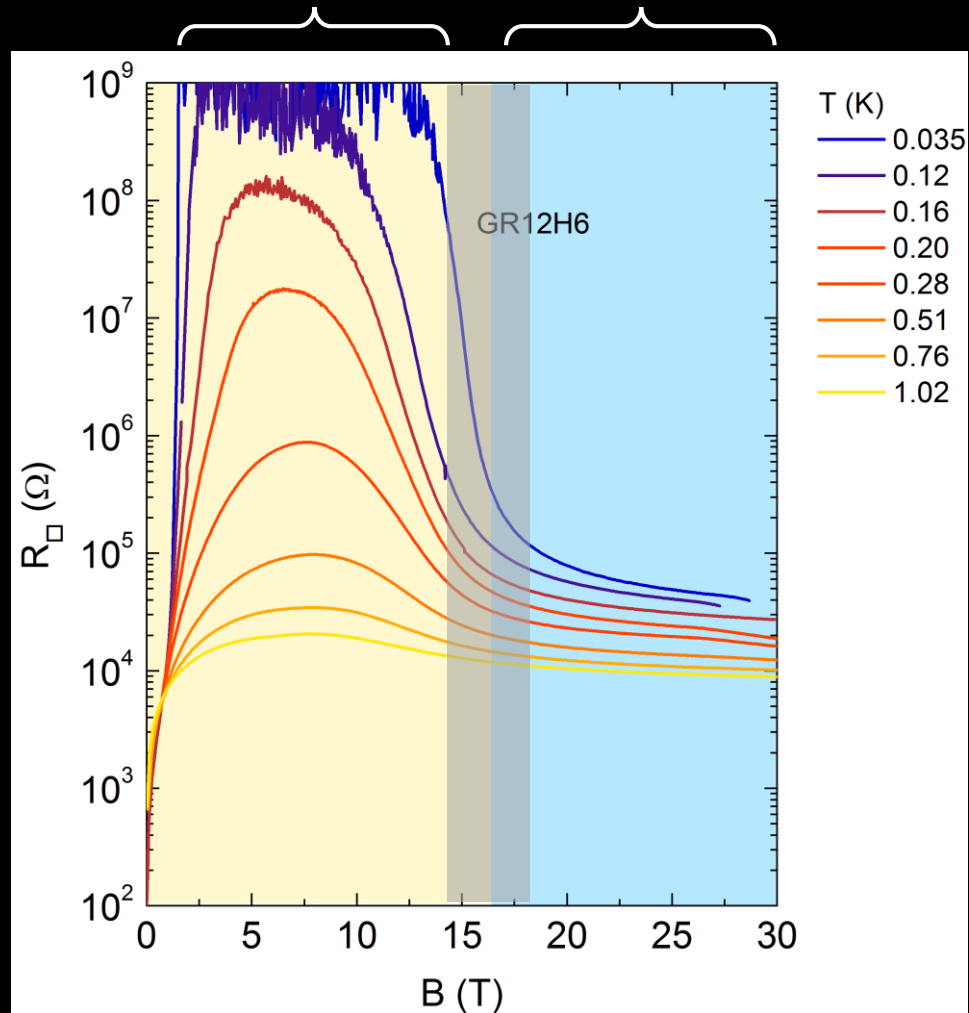
High disorder: Insulating peak



End of Cooper-pairing



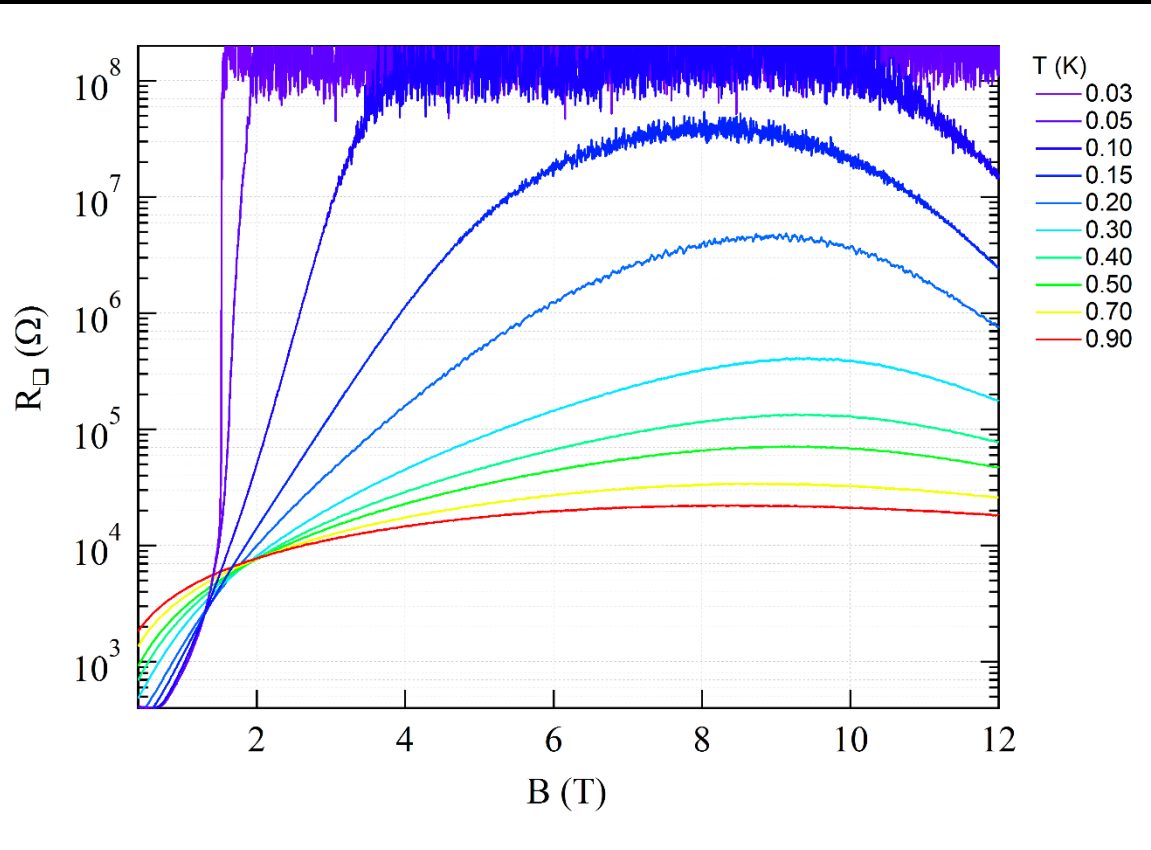
Cooper-pair insulator | Fermionic insulator



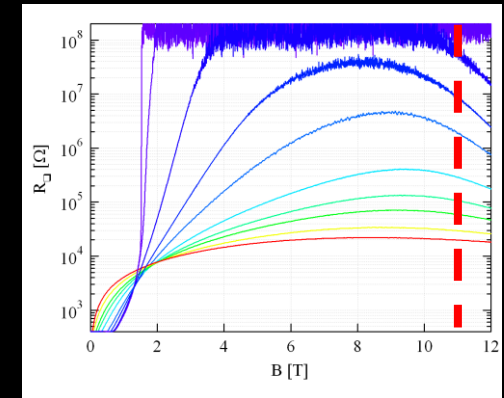
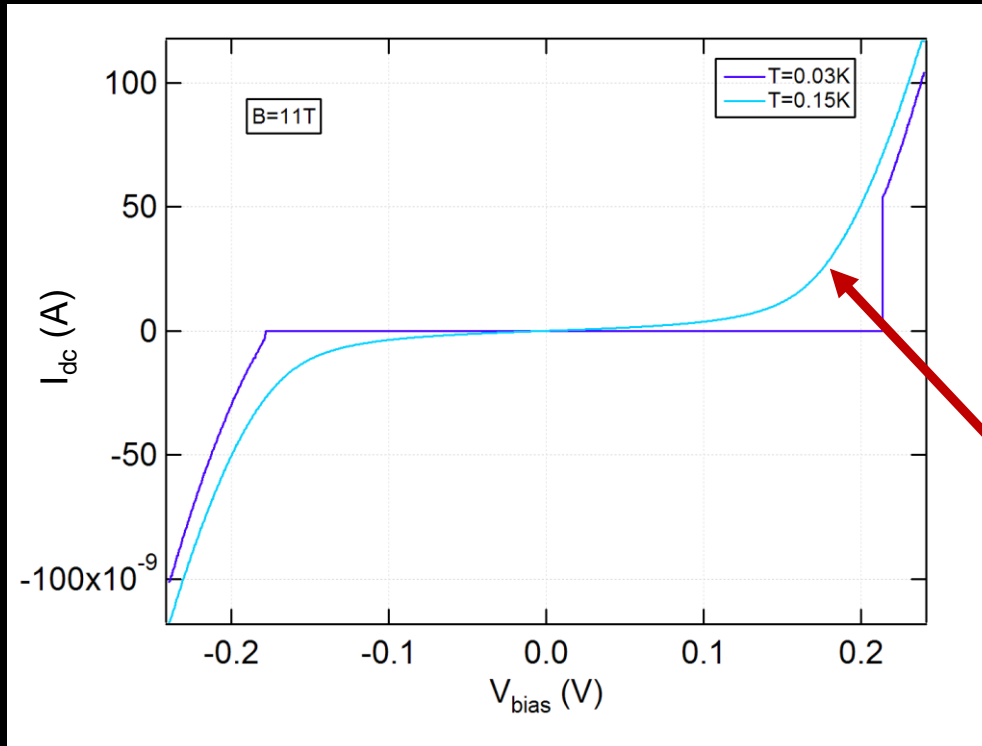
The insulator at $T < 0.2$ K

Current–voltage characteristics

Insulating peak

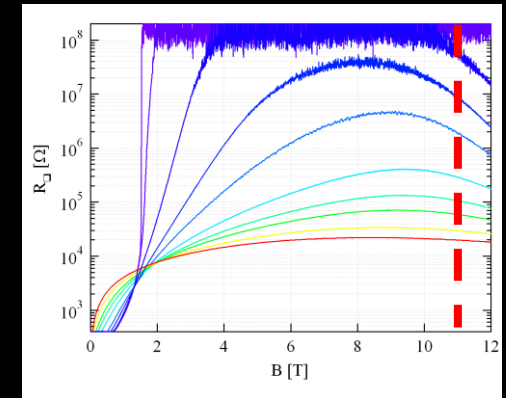
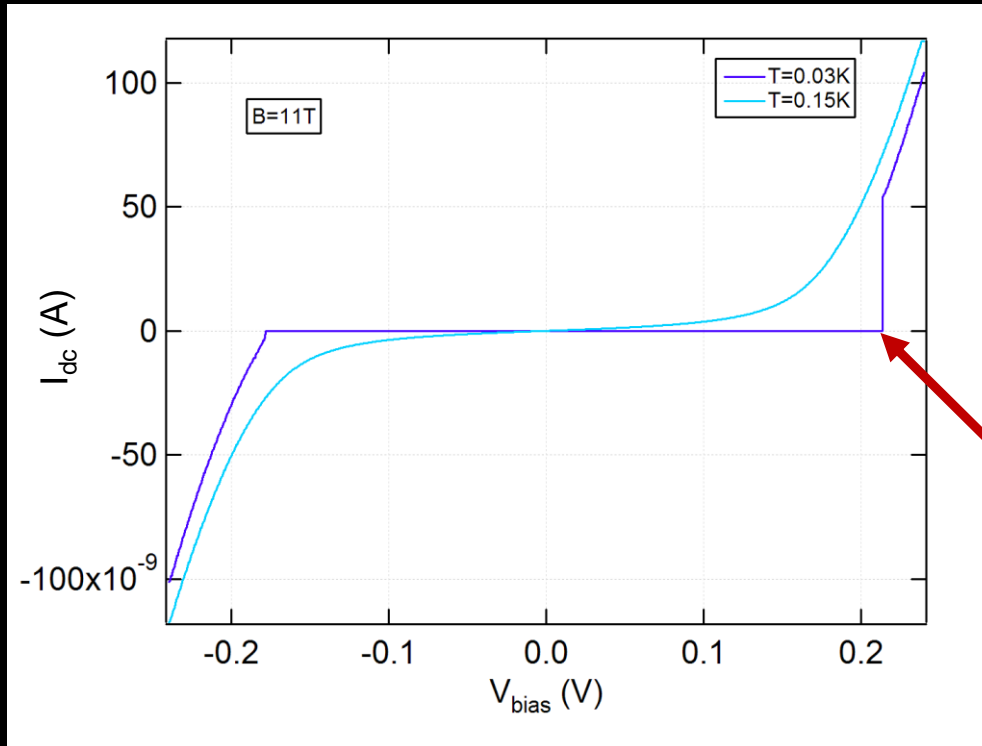


Non-linear IVs and voltage threshold



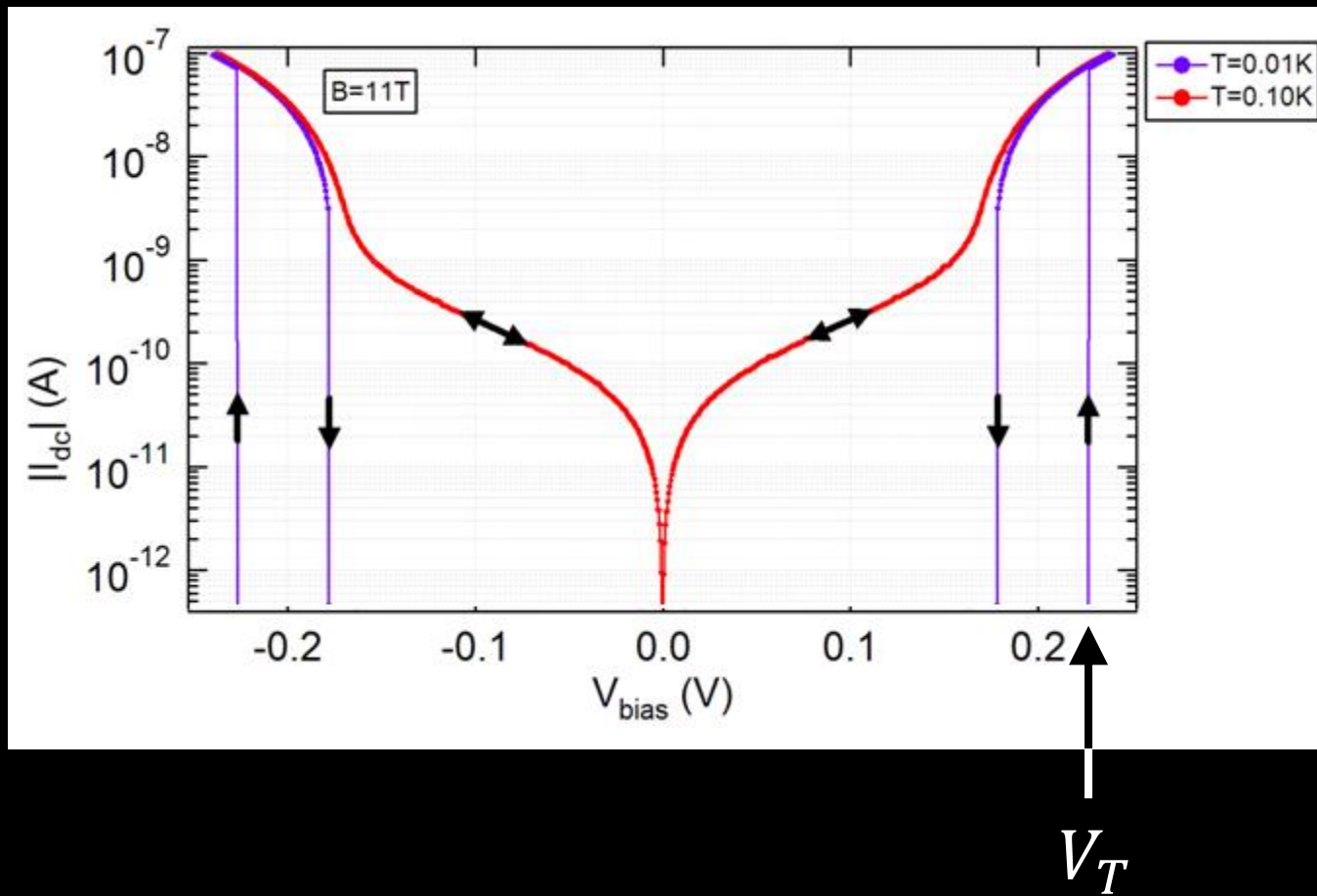
Non linear IV

Non-linear IVs and voltage threshold

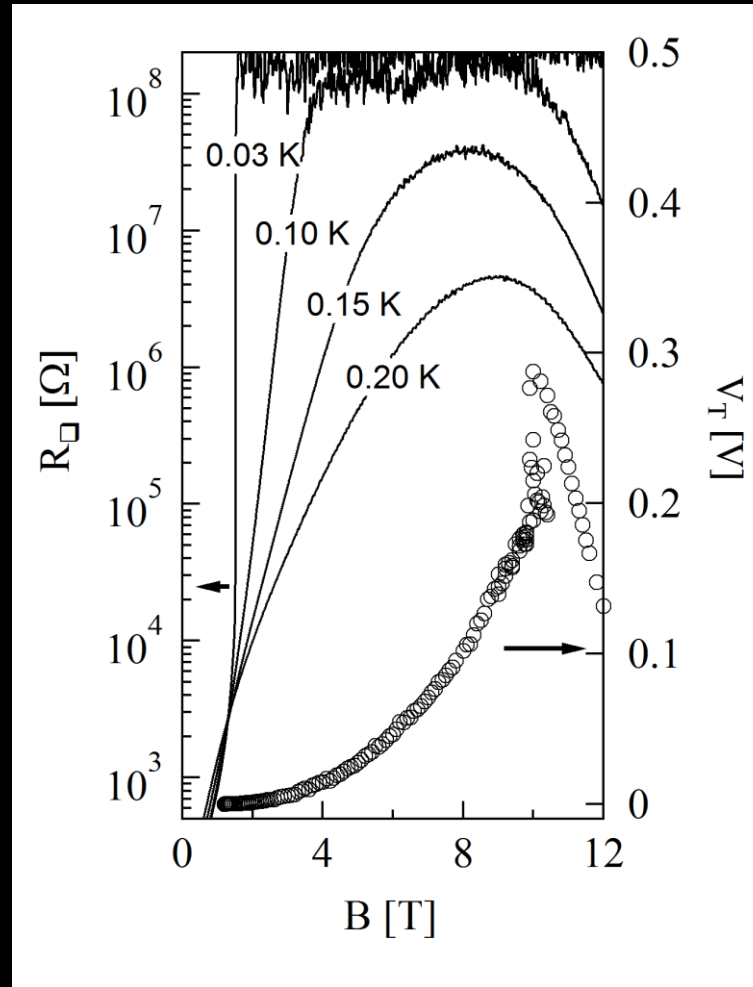


Voltage threshold

Transition to abrupt IV



Voltage threshold



Experimental Evidence for a Collective Insulating State in Two-Dimensional Superconductors

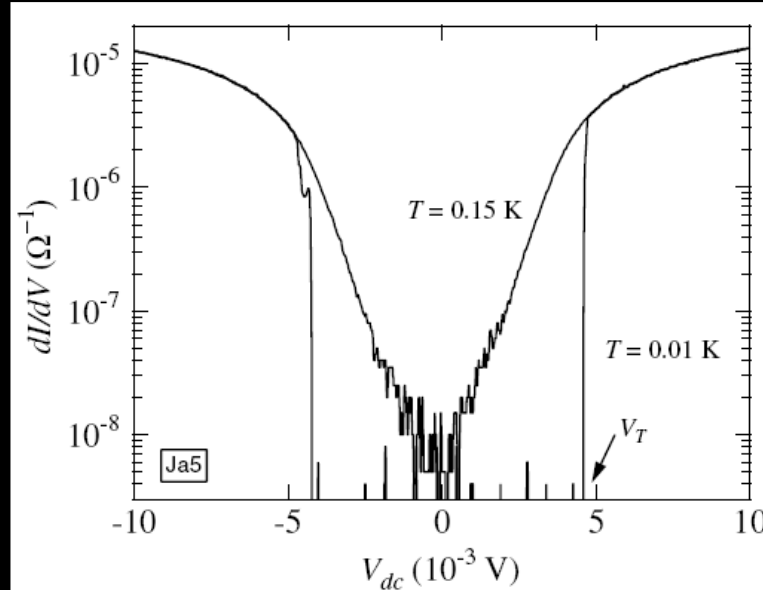
G. Sambandamurthy,¹ L. W. Engel,² A. Johansson,¹ E. Peled,¹ and D. Shahar¹

¹Department of Condensed Matter Physics, Weizmann Institute of Science, Rehovot 76100, Israel,

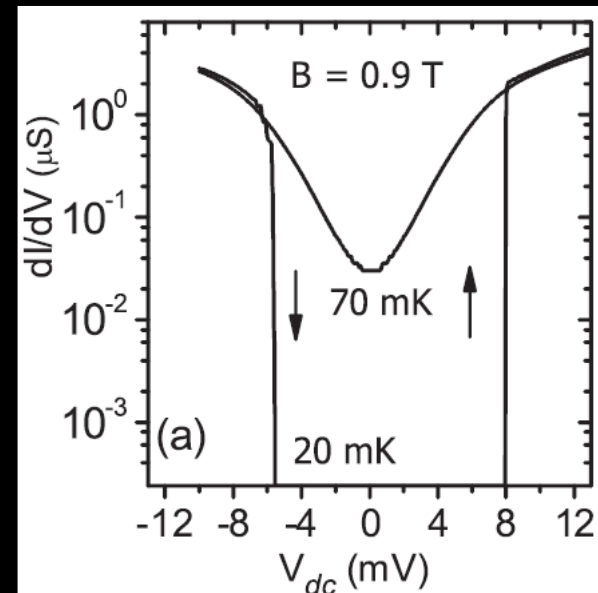
²National High Magnetic Field Laboratory, Florida State University, Tallahassee, Florida 32306, USA

(Received 18 March 2004; published 12 January 2005)

a:InO_x



TiN



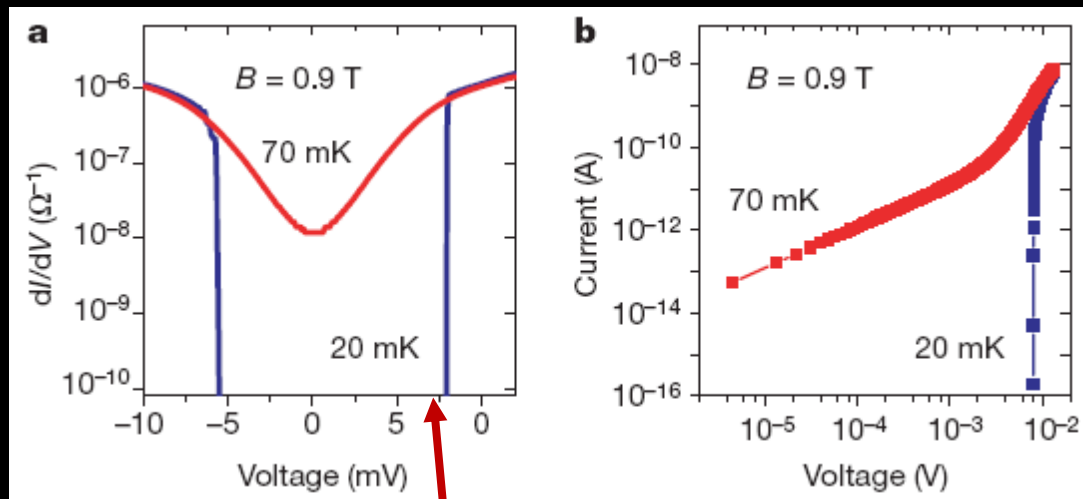
Baturina et al. PRL **99**, 257003 (2007)

Dramatic transition occurs around $T^* \sim 0.1$ K

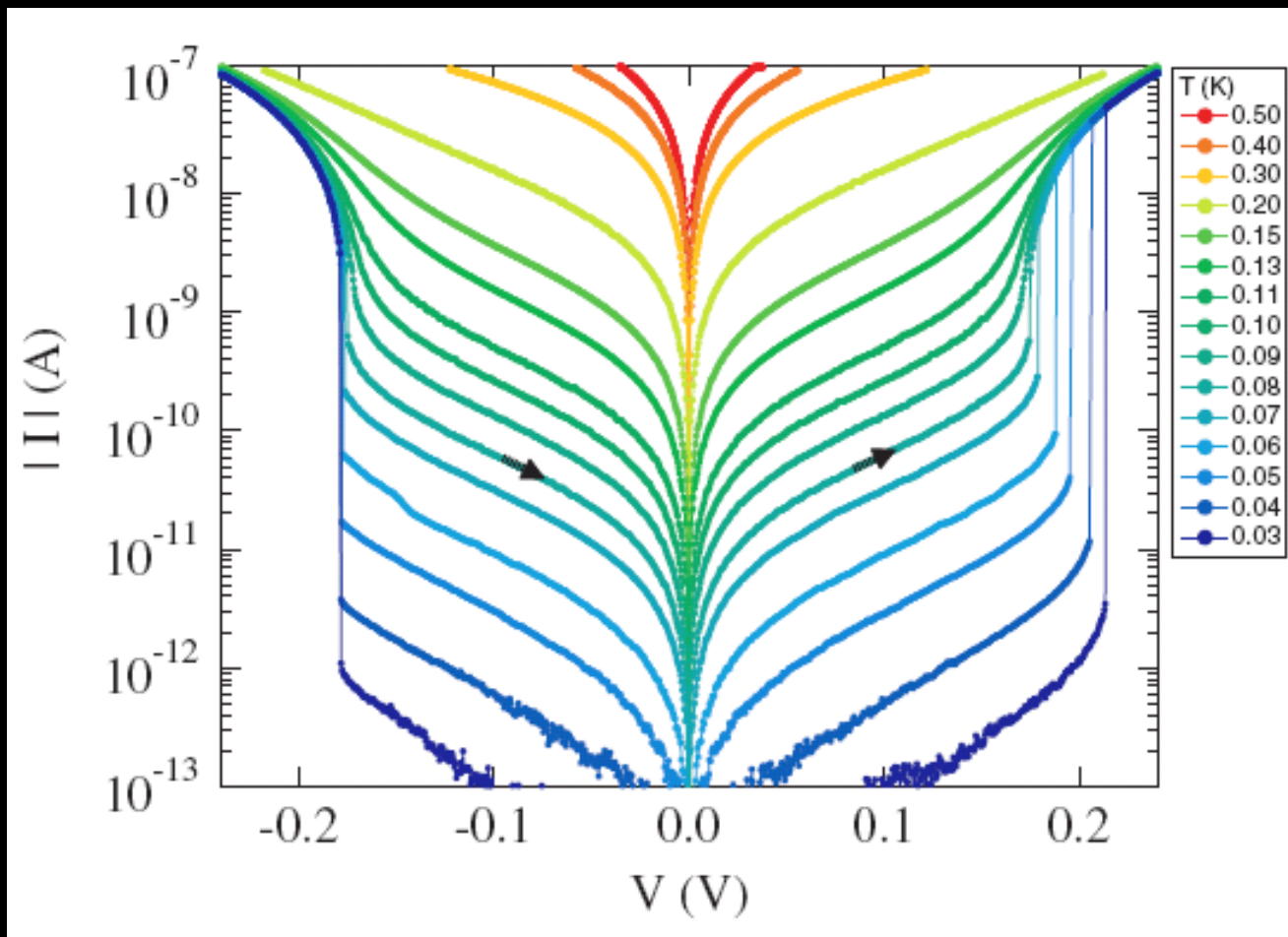
Superinsulator and quantum synchronization

Valerii M. Vinokur¹, Tatyana I. Baturina^{1,2,3}, Mikhail V. Fistul⁴, Aleksey Yu. Mironov^{2,3}, Mikhail R. Baklanov⁵ & Christoph Strunk³

NATURE 452, 613 (2008)



$G=0$ below V_T !?





Jumps in Current-Voltage Characteristics in Disordered Films

Boris L. Altshuler,^{1,2} Vladimir E. Kravtsov,³ Igor V. Lerner,⁴ and Igor L. Aleiner¹

Hysteresis \longrightarrow **electron overheating**



Jumps in Current-Voltage Characteristics in Disordered Films

Boris L. Altshuler,^{1,2} Vladimir E. Kravtsov,³ Igor V. Lerner,⁴ and Igor L. Aleiner¹

1. Electrons and phonons are decoupled
2. Electrons are strongly interacting (can have $T_{el} \neq T_{ph}$)
3. Intrinsic I-V is linear: heating is the only source of non-linearity
4. R is a fast function of electron temperature

$$R(T_{el}) = R_0 e^{(T_0/T_{el})^\gamma}, \text{ with } \gamma \leq 1$$



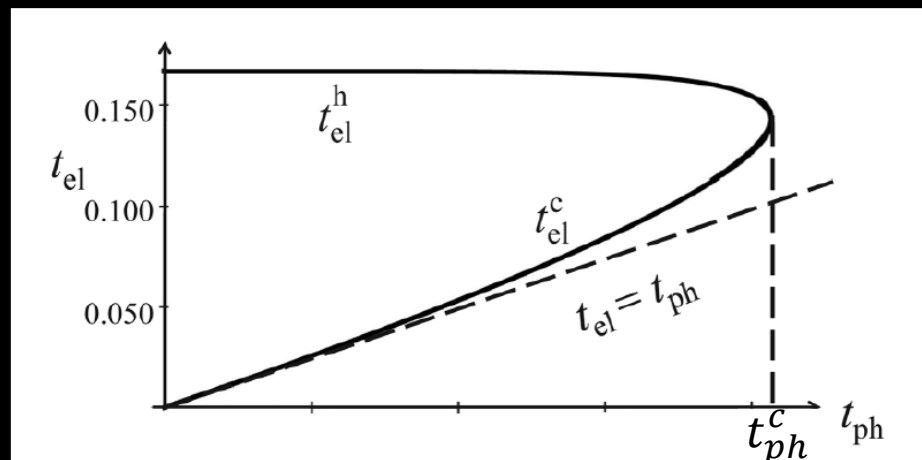
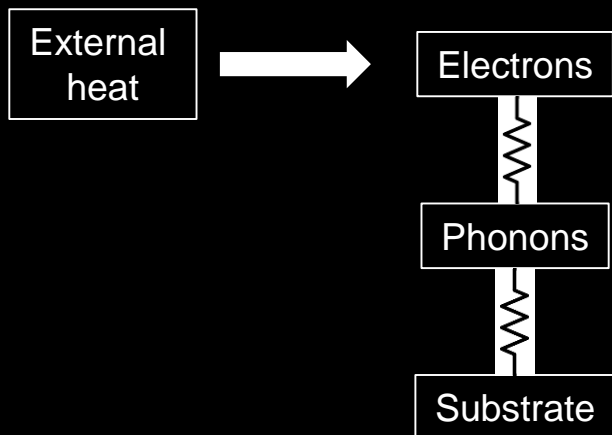
Jumps in Current-Voltage Characteristics in Disordered Films

Boris L. Altshuler,^{1,2} Vladimir E. Kravtsov,³ Igor V. Lerner,⁴ and Igor L. Aleiner¹

Heat balance equation :

$$\frac{V^2}{R(T_{el})} = \Gamma \Omega (T_{el}^6 - T_{ph}^6)$$

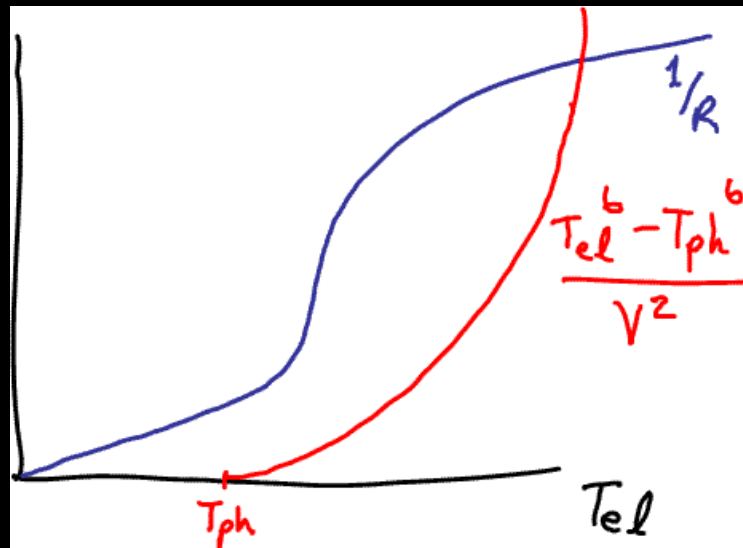
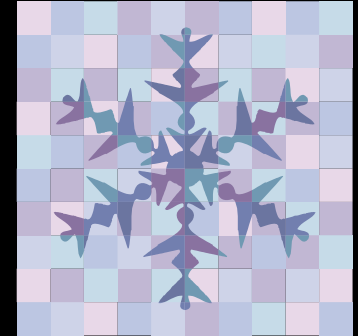
$$R(T_{el}) = R_0 e^{(T_0/T_{el})^\gamma}$$



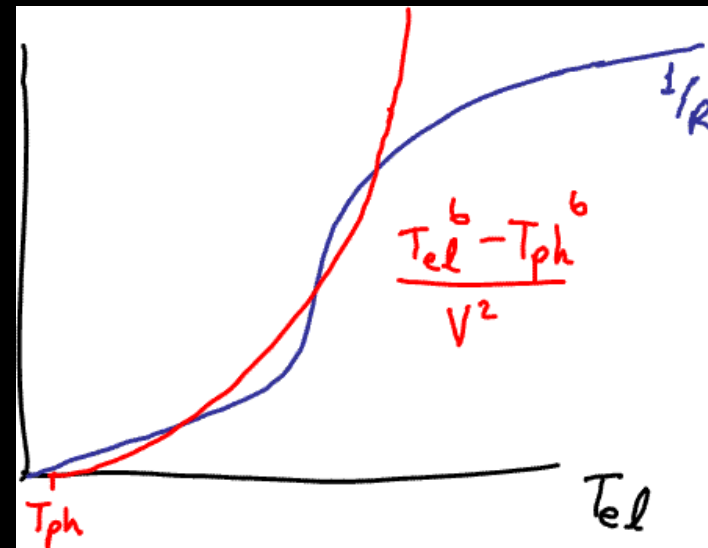
Lowering T_{phonon}

$$\frac{1}{R(T_{el})} = \frac{\Gamma\Omega(T_{el}^6 - T_{ph}^6)}{V^2}$$

$$R(T_{el}) = R_0 e^{\Delta/T}$$

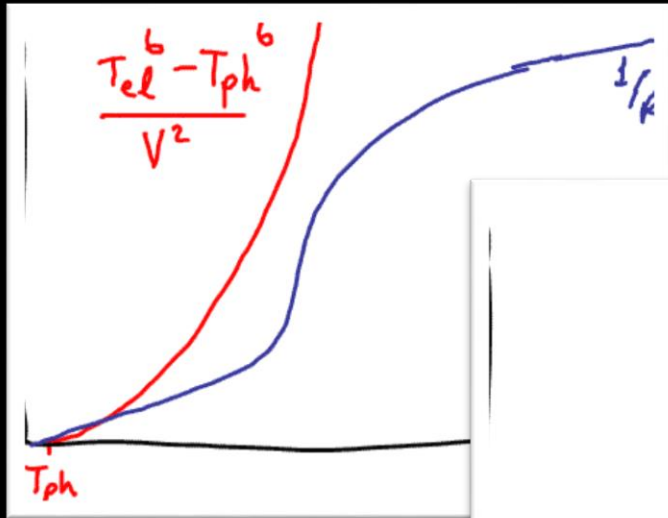


One solution at $T_{el} > T_{ph}$

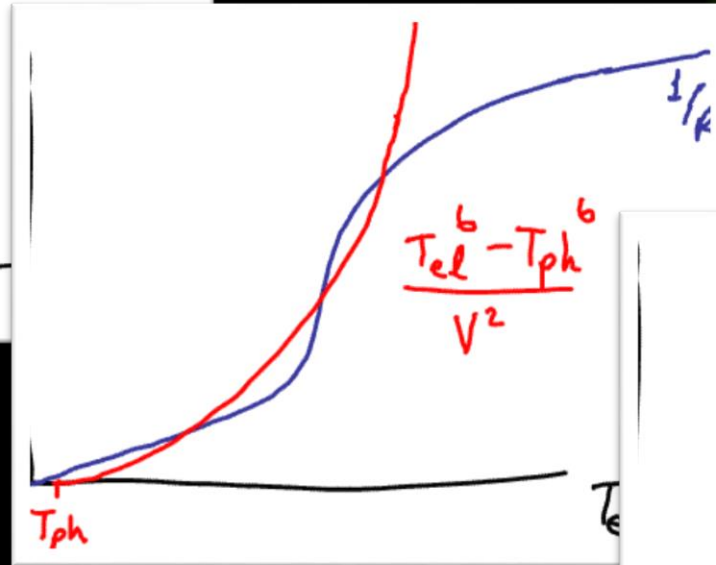


Multiple solutions for T_{el}

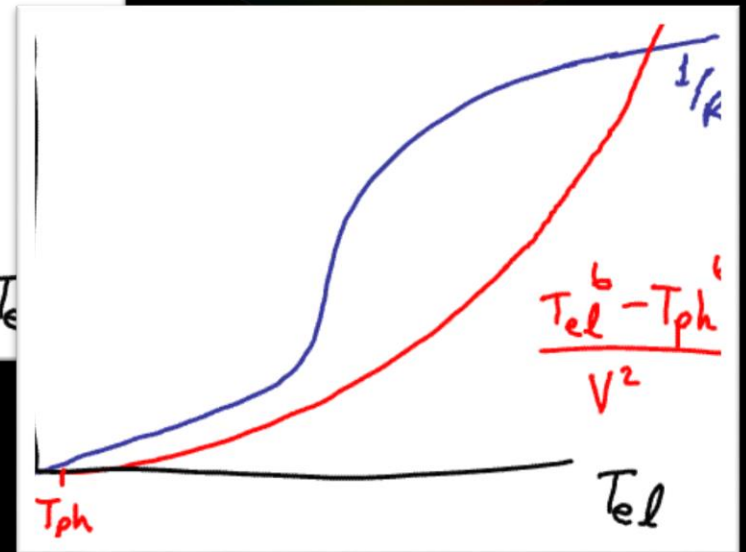
Changing voltage...



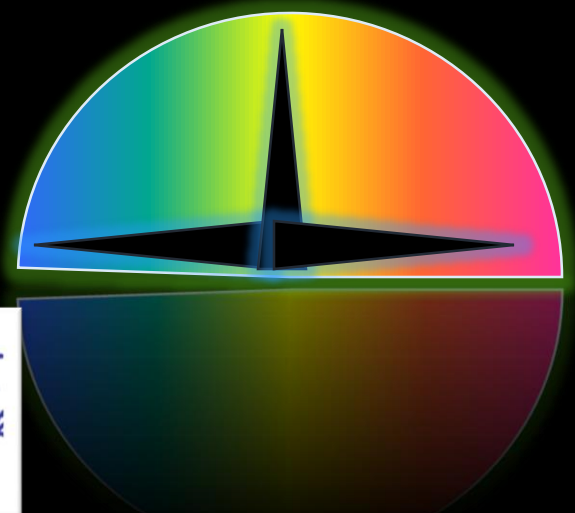
Single solution
at $T_{el} \sim T_{ph}$



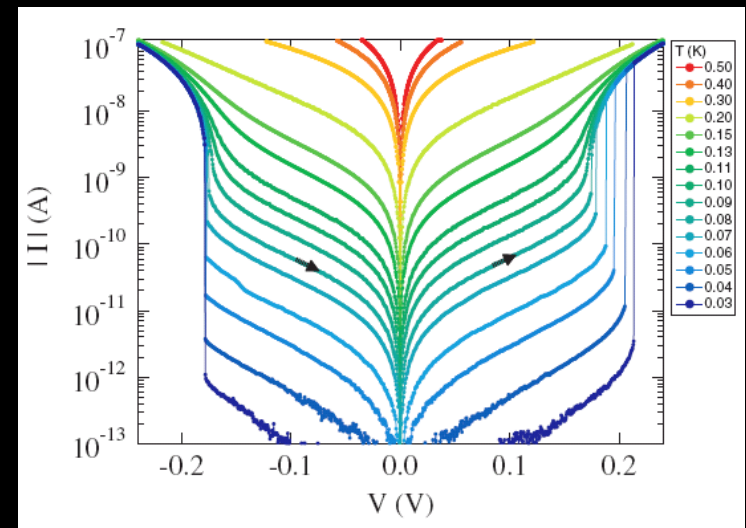
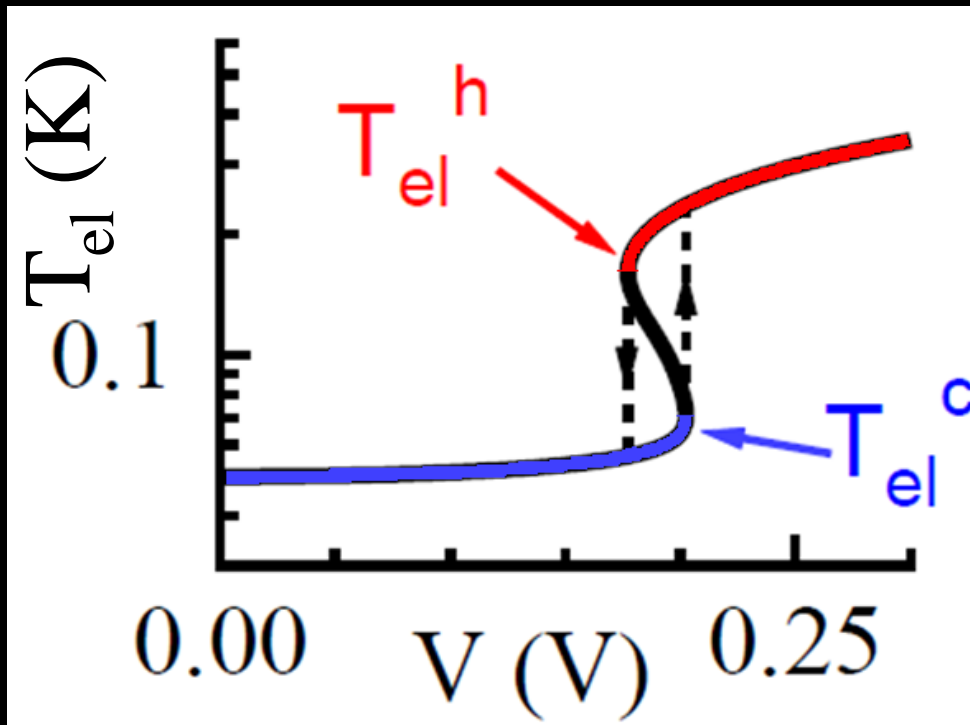
Multiple solutions



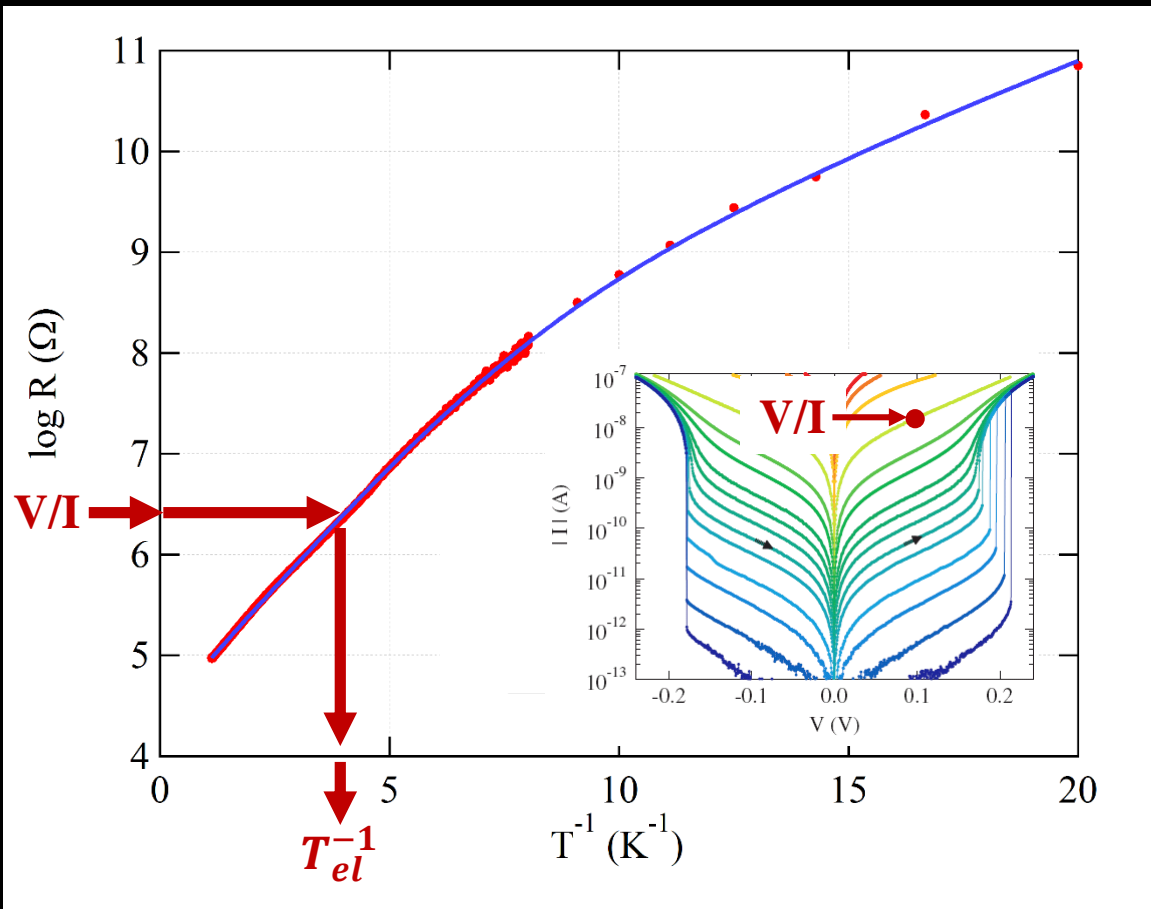
Single solution
at $T_{el} > T_{ph}$



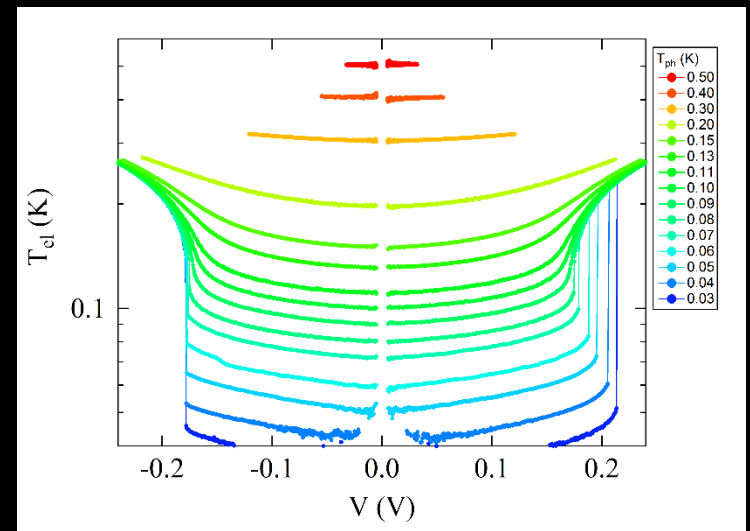
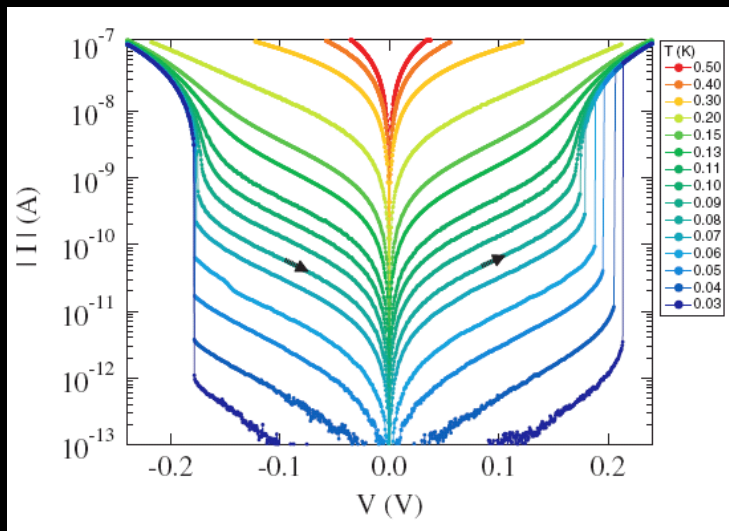
Thermal bi-stability



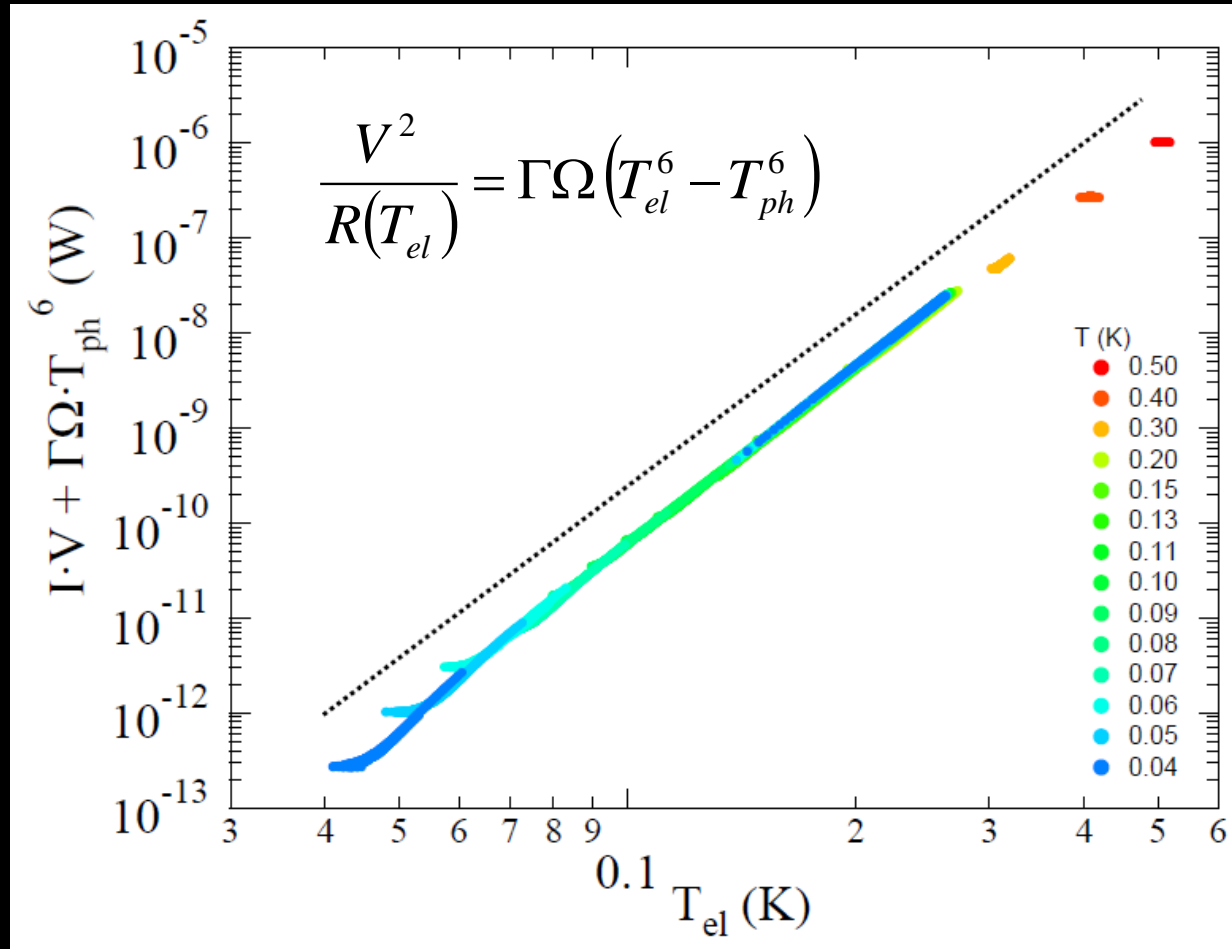
Determine T_{el}



Determine T_{el}

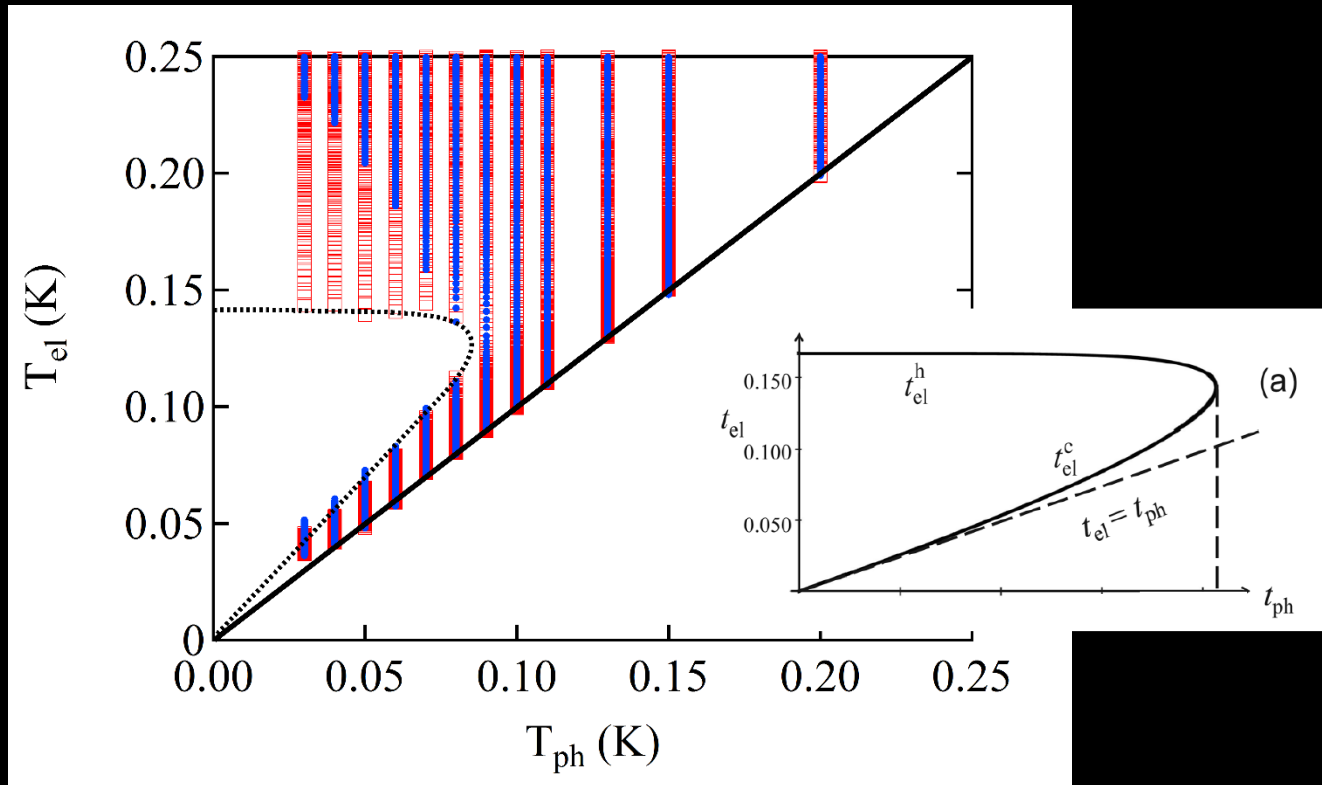


Electron overheating

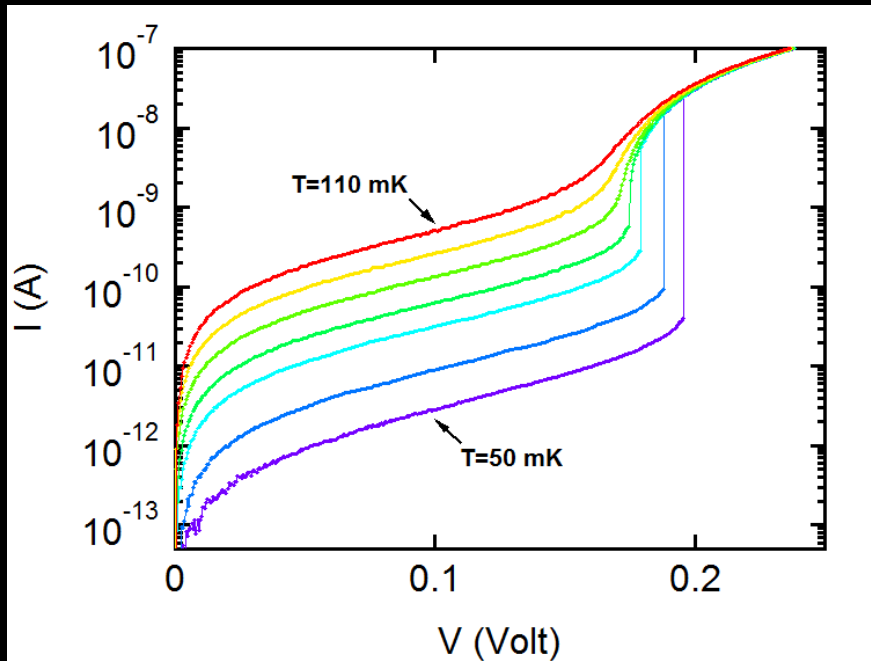


Assume hot-electron scenario \Rightarrow recover heat balance equation !

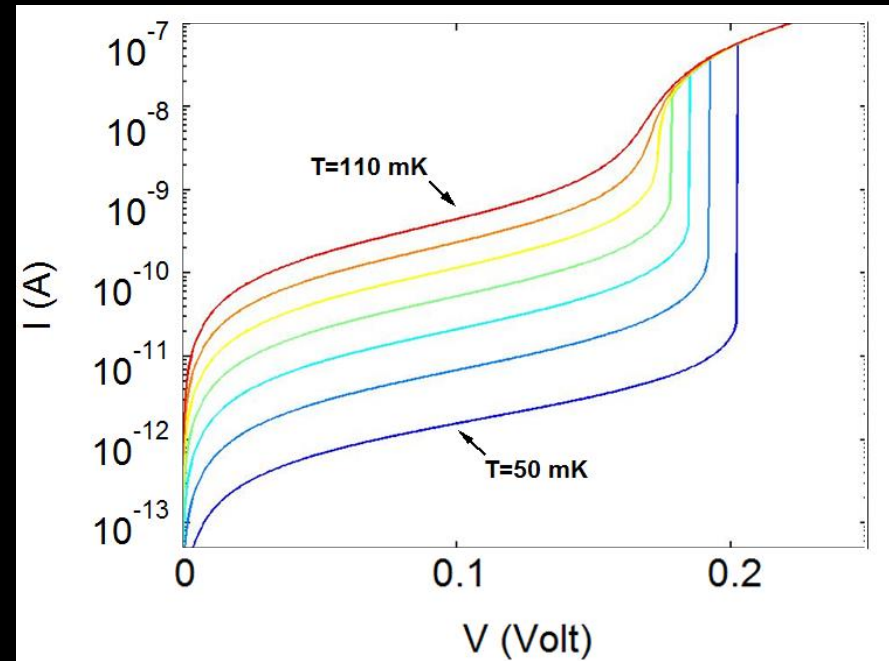
Excluded region



IV's computed with $R(T)$ curve and heat balance equation

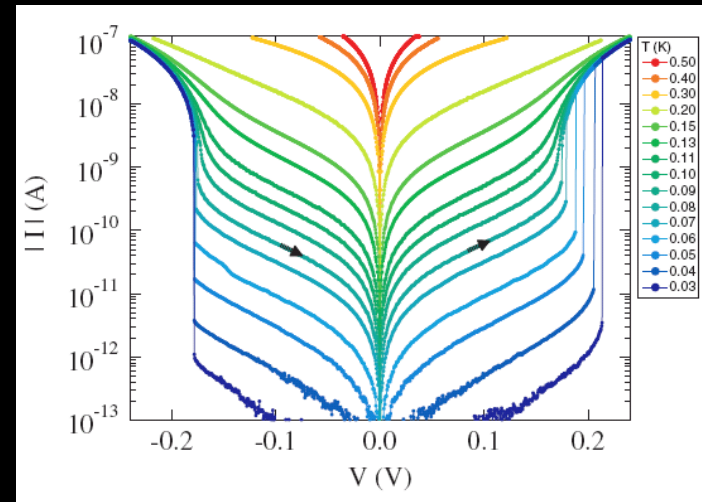
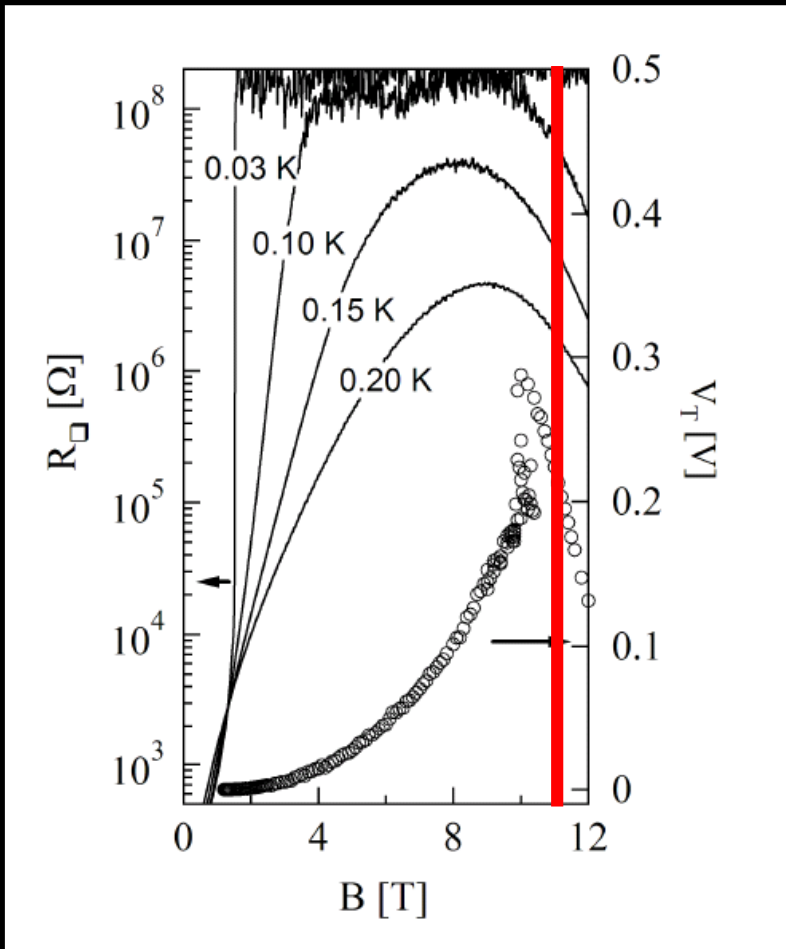


M. Ovadia, B. Sacépé, and D. Shahar
Phys. Rev. Lett. 102, 176802 (2009)



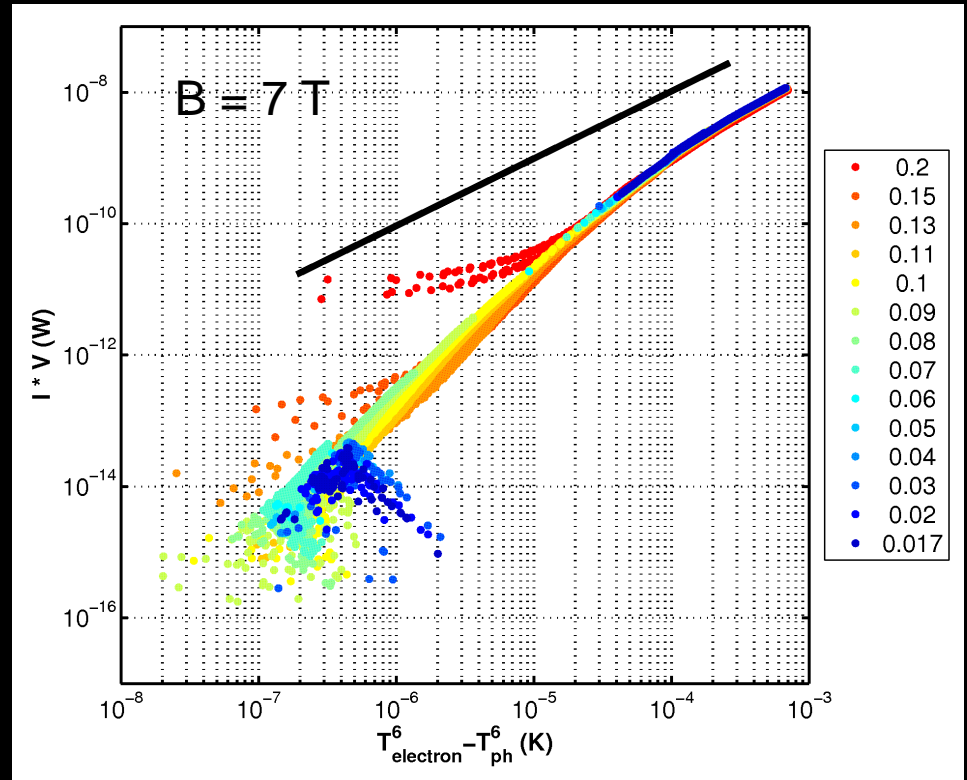
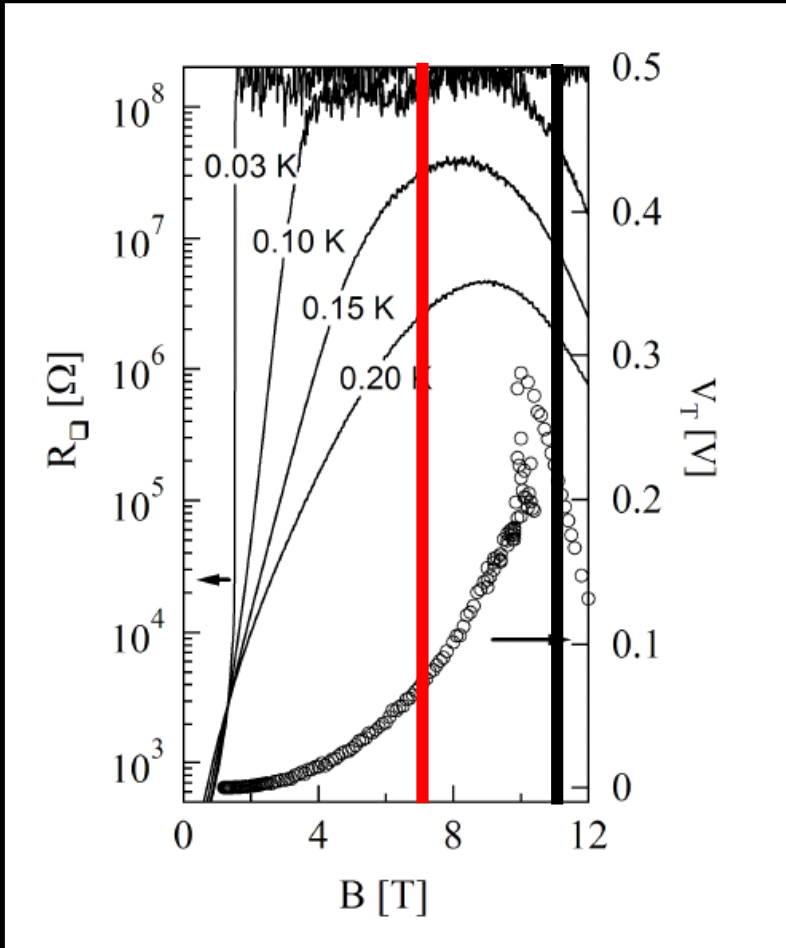
B. Altshuler, V. Kravtsov, I. Lerner, and I. Aleiner
Phys. Rev. Lett. 102, 176803 (2009)

Heating at B = 11 T



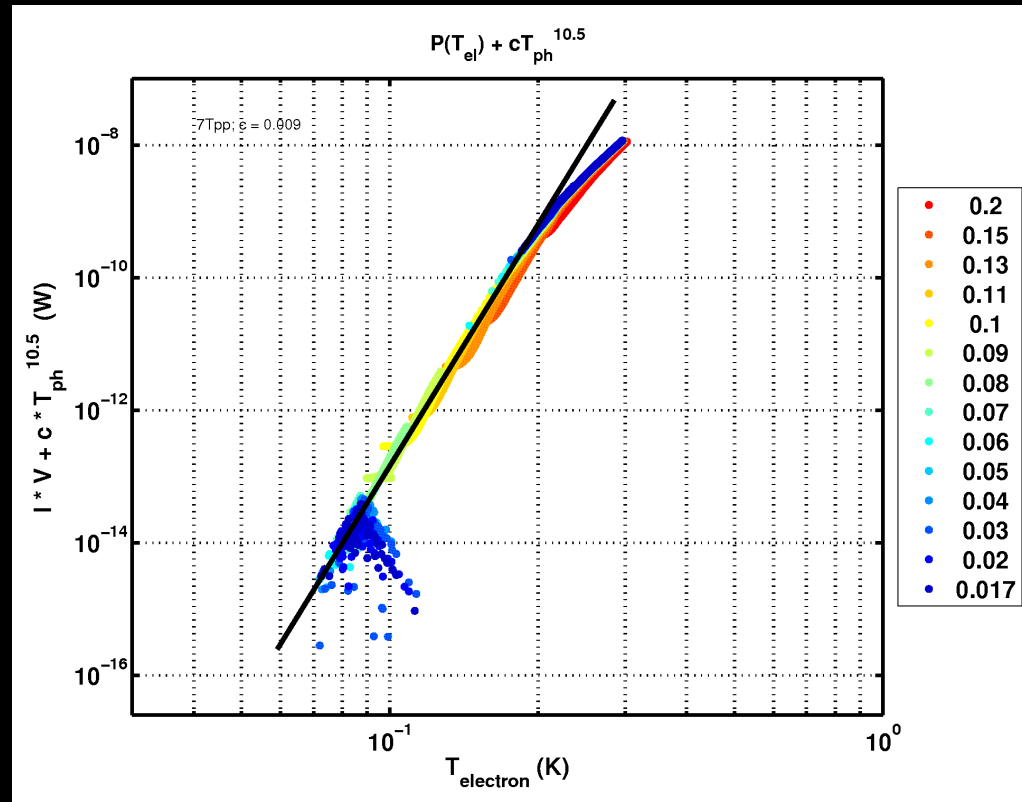
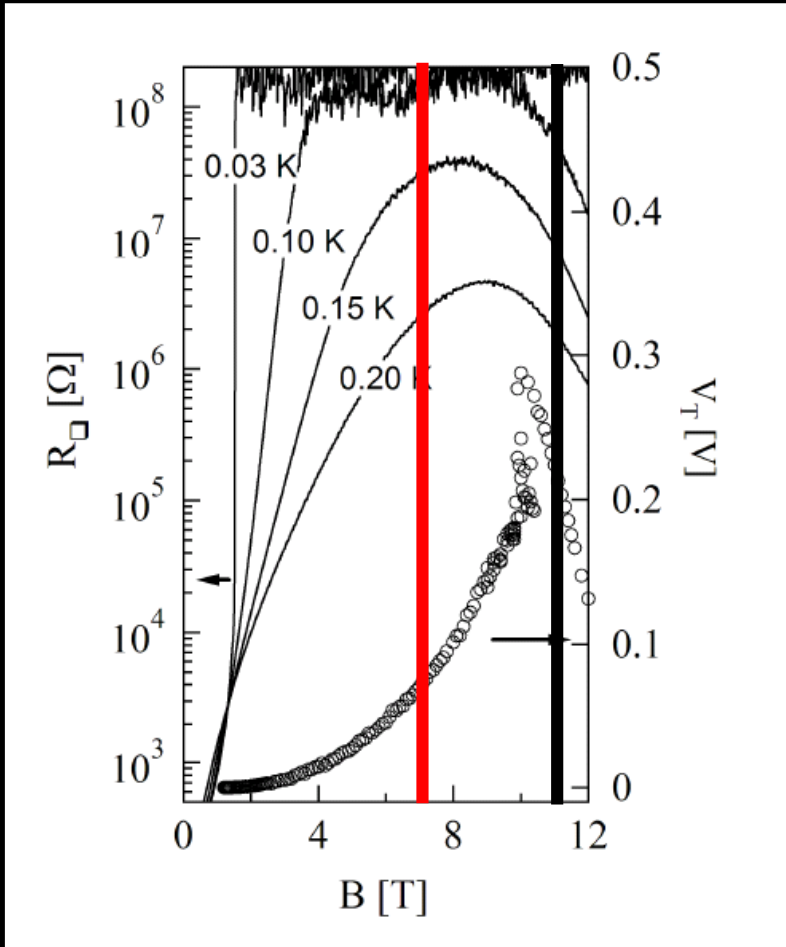
$$\frac{V^2}{R(T_{el})} = \Gamma \Omega (T_{el}^6 - T_{ph}^6)$$

Heating at lower field



~~$$\frac{V^2}{R(T_{el})} = \Gamma \Omega (T_{el}^6 - T_{ph}^6)$$~~

Heating at lower field

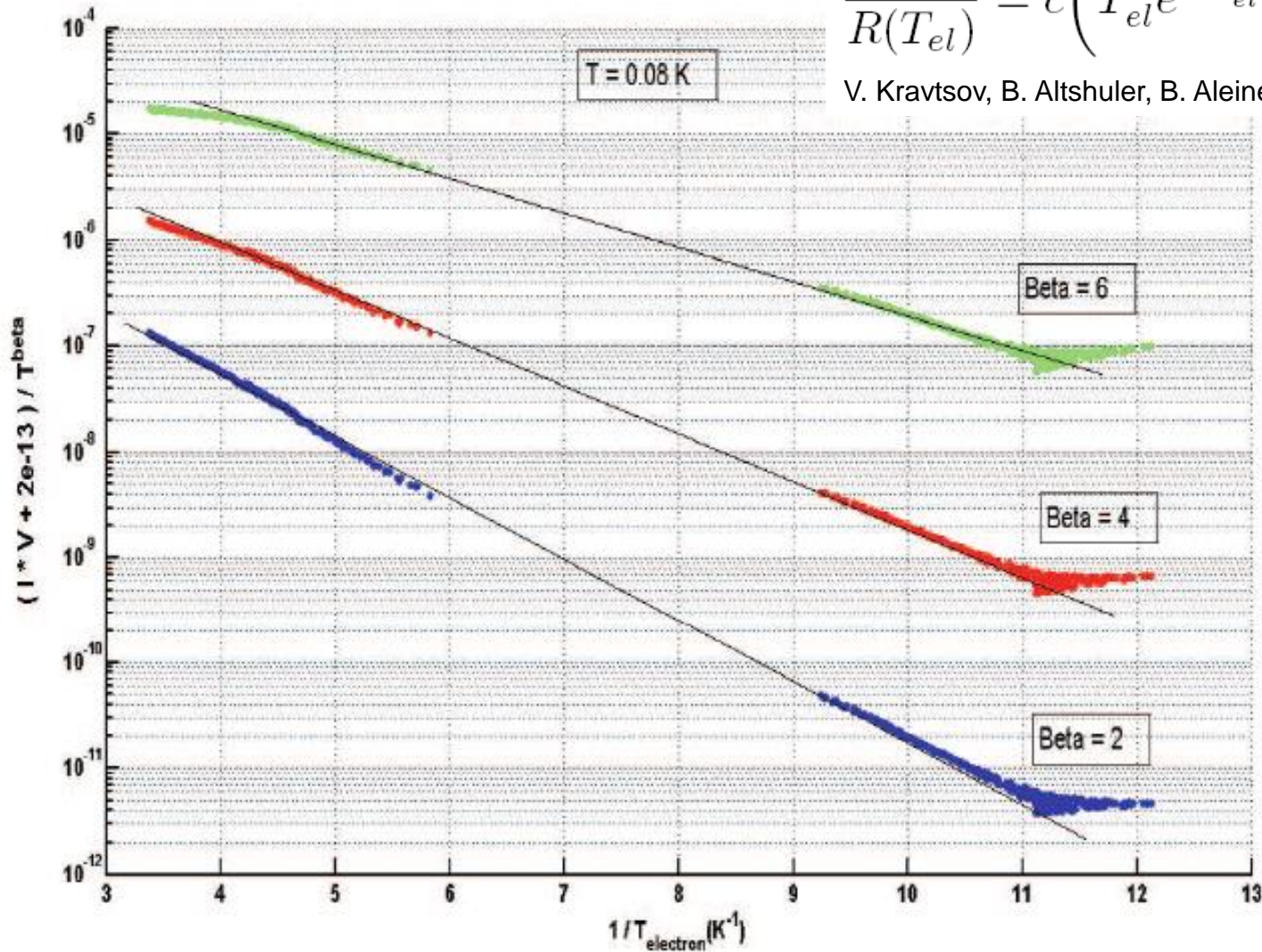


$$\frac{V^2}{R(T_{el})} = \Gamma \Omega (T_{el}^\alpha - T_{ph}^\alpha), \quad \alpha > 10 \text{ ???}$$

Exponentially suppressed cooling rate at B=7T

$$\frac{V^2}{R(T_{el})} = c \left(T_{el}^\beta e^{-\frac{\Delta_d}{T_{el}}} - T_{ph}^\beta e^{-\frac{\Delta_d}{T_{ph}}} \right),$$

V. Kravtsov, B. Altshuler, B. Aleiner, unpublished



For beta=4
 $\Delta_d = 0.97 K$

Conclusion on non-linear transport

- ☑ Charge carriers are interacting and **form a bath at T_{el}**
- ☑ Charge carriers and phonons are **weakly coupled**
- ☑ *IV* non-linearities due to **electron overheating**



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Annals of Physics 321 (2006) 1126–1205

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Metal–insulator transition in a weakly interacting many-electron system with localized single-particle states

D.M. Basko^{a,b,*}, I.L. Aleiner^b, B.L. Altshuler^{a,b,c}

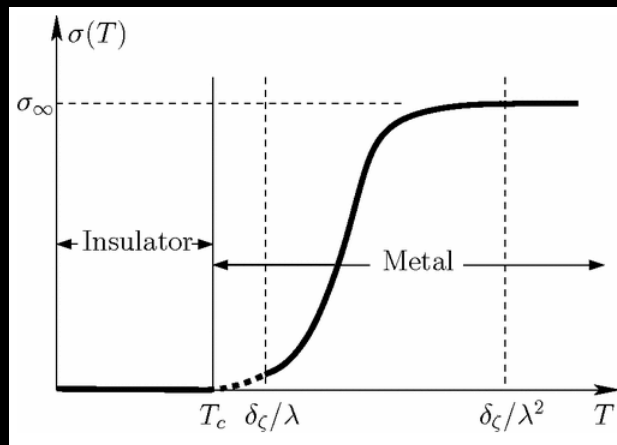
^a *Department of Physics, Princeton University, Princeton, NJ 08544, USA*

^b *Physics Department, Columbia University, New York, NY 10027, USA*

^c *NEC-Laboratories America, 4 Independence Way, Princeton, NJ 085540, USA*

Received 14 August 2005; accepted 30 November 2005

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$$\begin{aligned}
[i\partial_{t_1} - \xi_l(\boldsymbol{\rho})]\hat{\mathcal{G}}_l(\boldsymbol{\rho}) &= \hat{\tau}_0\delta(t_1 - t_2) + \hat{\Sigma}_l(\boldsymbol{\rho}) \circ \hat{\mathcal{G}}_l(\boldsymbol{\rho}); \\
[-i\partial_{t_2} - \xi_l(\boldsymbol{\rho})]\hat{\mathcal{G}}_l(\boldsymbol{\rho}) &= \hat{\tau}_0\delta(t_1 - t_2) + \hat{\mathcal{G}}_l(\boldsymbol{\rho}) \circ \hat{\Sigma}_l(\boldsymbol{\rho}); \\
\hat{\mathcal{G}} &= \begin{bmatrix} \mathcal{G}_l^R(\boldsymbol{\rho}) & \mathcal{G}_l^K(\boldsymbol{\rho}) \\ 0 & \mathcal{G}_l^A(\boldsymbol{\rho}) \end{bmatrix}_K; \quad \hat{\Sigma} = \begin{bmatrix} \Sigma_l^R(\boldsymbol{\rho}) & \Sigma_l^K(\boldsymbol{\rho}) \\ 0 & \Sigma_l^A(\boldsymbol{\rho}) \end{bmatrix}_K; \\
\hat{\tau}^0 &= \begin{bmatrix} 1 & 0 \\ 0 & 1 \end{bmatrix}_K; \quad \hat{\tau}^2 = \begin{bmatrix} 0 & 1 \\ 1 & 0 \end{bmatrix}_K.
\end{aligned}$$

$$\overleftarrow{\mu_1} \xrightarrow{(l, \rho)} \mu_2 = i [\hat{\mathcal{G}}_l(\boldsymbol{\rho})]_{\mu_1 \mu_2} = i \begin{bmatrix} G_l^R(\boldsymbol{\rho}) & G_l^K(\boldsymbol{\rho}) \\ 0 & G_l^A(\boldsymbol{\rho}) \end{bmatrix}_{\mu_1 \mu_2}$$

$$\begin{aligned}
\overleftarrow{\mu_1} \not\xrightarrow{(l, \rho)} \mu_2 &= \overleftarrow{\mu_1} \xrightarrow{(l', \rho') \neq (l, \rho)} \mu_2 & G_l^R(\boldsymbol{\rho}) &= [G_l^A(\boldsymbol{\rho})]^* = \frac{1}{\epsilon - \xi_l(\boldsymbol{\rho}) + i0^+} \\
& & G_l^K(\boldsymbol{\rho}) &= -2\pi i n_l(\boldsymbol{\rho}, \epsilon) \delta[\epsilon - \xi_l(\boldsymbol{\rho})]
\end{aligned}$$

B

$$\overleftarrow{\mu_1} \xrightarrow{(l, \rho)} \mu_2 = i [\hat{\mathcal{G}}_l(\boldsymbol{\rho})]_{\mu_1 \mu_2};$$

C

$$\overleftarrow{\mu_1} \xrightarrow{(l_1, \rho_1)} \mu_1 \text{ --- } \mu_2 \xrightarrow{(l_2, \rho_2)} \mu_2 = -iI\delta_\xi [\hat{\tau}^0]_{\mu_1 \mu_2} (\boldsymbol{\rho}_1, \boldsymbol{\rho}_2)_{nn};$$

D

$$\begin{aligned}
& \begin{array}{c} (j_1, \rho_1) \\ \mu_2 \\ \downarrow \\ (l_1, \rho) \quad \mu_1 \leftarrow \quad \rightarrow \quad \mu_4 \quad (l_2, \rho) \\ \swarrow \quad \searrow \\ (j_2, \rho_2) \quad \mu_3 \uparrow \end{array} = -\frac{i}{2} V_{l_1 l_2}^{j_1 j_2}(\boldsymbol{\rho}) \left([\hat{\tau}^2]_{\mu_1 \mu_2} [\hat{\tau}^0]_{\mu_3 \mu_4} + [\hat{\tau}^2]_{\mu_1 \mu_2} [\hat{\tau}^0]_{\mu_3 \mu_4} \right)
\end{aligned}$$

E

$$\overleftarrow{\mu_1} \xrightarrow{(l, \rho)} \mu_2 = \overleftarrow{\mu_1} \xrightarrow{(l, \rho)} \mu_2 + \overleftarrow{\mu_1} \xrightarrow{(l, \rho)} \mu_2 \text{ (hexagon)} + \overleftarrow{\mu_1} \xrightarrow{(l, \rho)} \mu_2 \text{ (circle)}$$

$$\text{(circle)} = -i\hat{\Sigma}_l(\boldsymbol{\rho}) = \text{Fig. 4} + \text{Fig. 5} + \dots$$

Possible experimental manifestations of the many-body localization

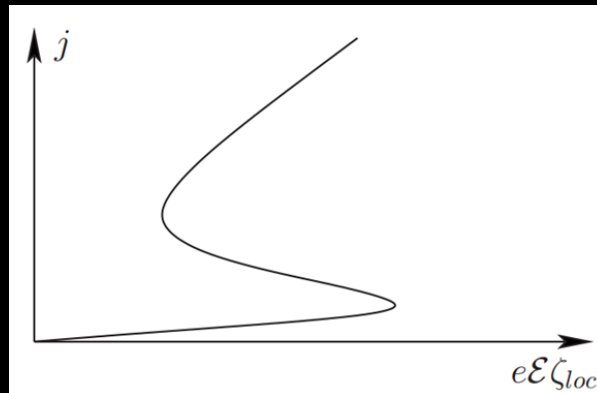
D. M. Basko,^{1,*} I. L. Aleiner,¹ and B. L. Altshuler^{1,2}

¹*Physics Department, Columbia University, New York, New York 10027, USA*

²*NEC-Laboratories America, Inc., 4 Independence Way, Princeton, New Jersey 08540, USA*

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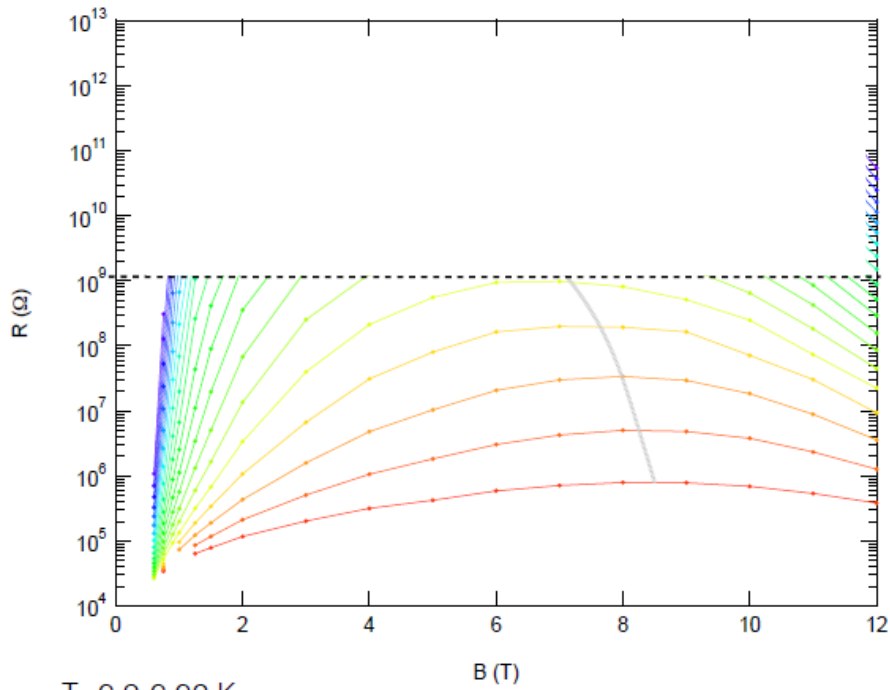
Recently, it was predicted that if all one-electron states in a noninteracting disordered system are localized, the interaction between electrons in the absence of coupling to phonons leads to a finite-temperature metal-insulator transition. Here, we show that even in the presence of a weak coupling to phonons the transition manifests itself (i) in the nonlinear conduction, leading to a bistable I - V curve, and (ii) by a dramatic enhancement of the nonequilibrium current noise near the transition.



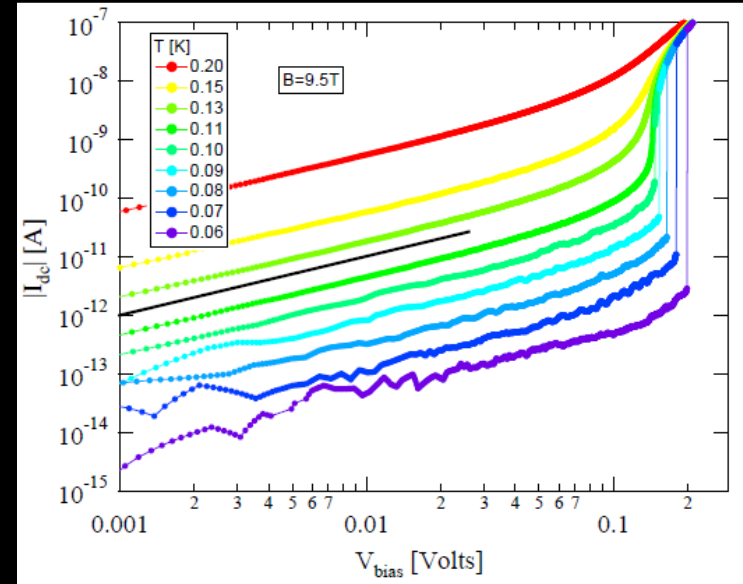
The insulator at $T < 0.2$ K

Ohmic transport

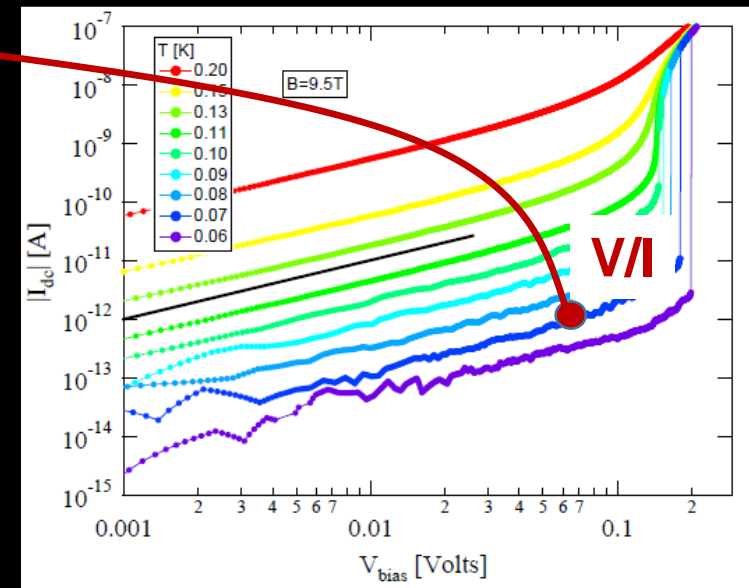
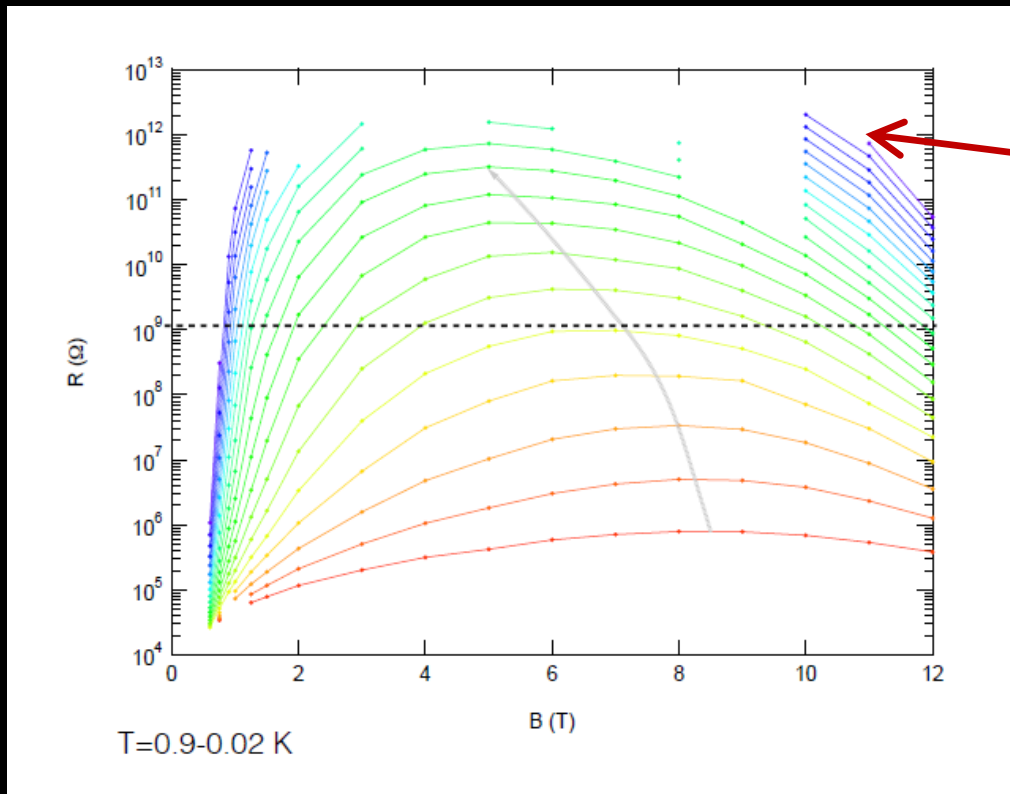
Ohmic transport



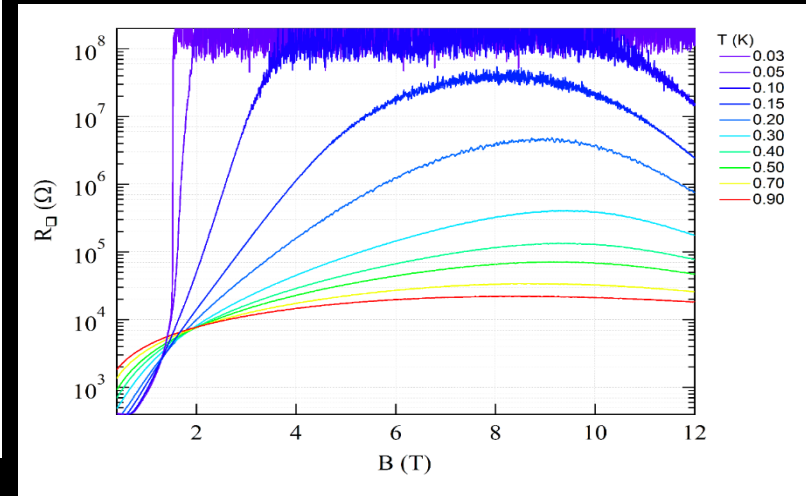
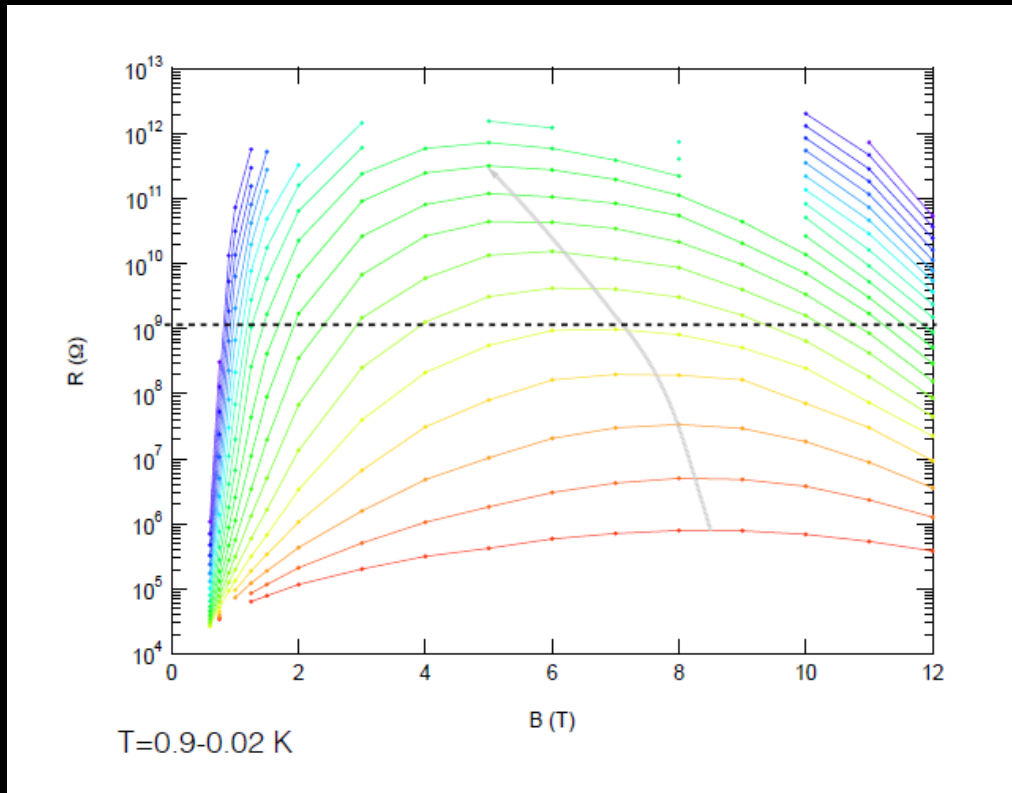
$T=0.9-0.02$ K



Ohmic transport

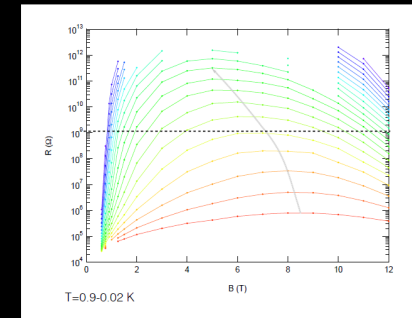
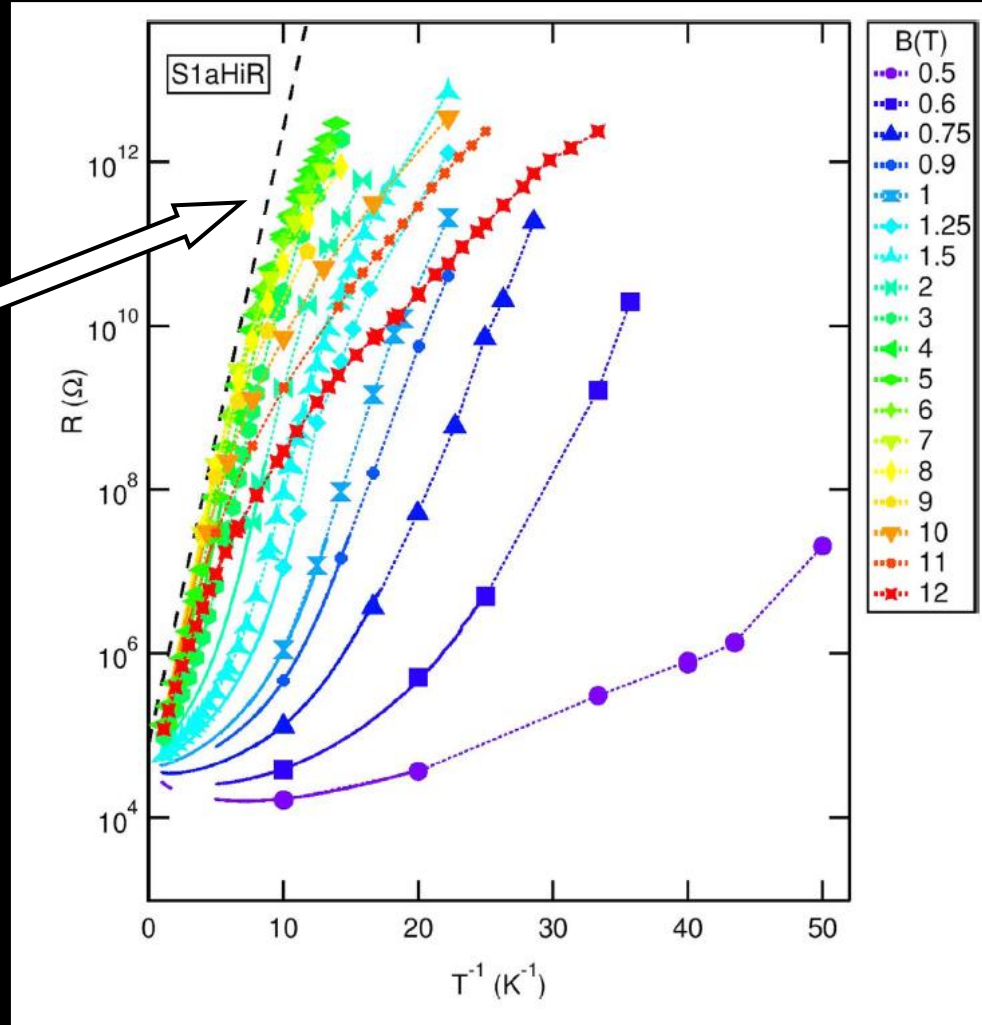


Ohmic transport

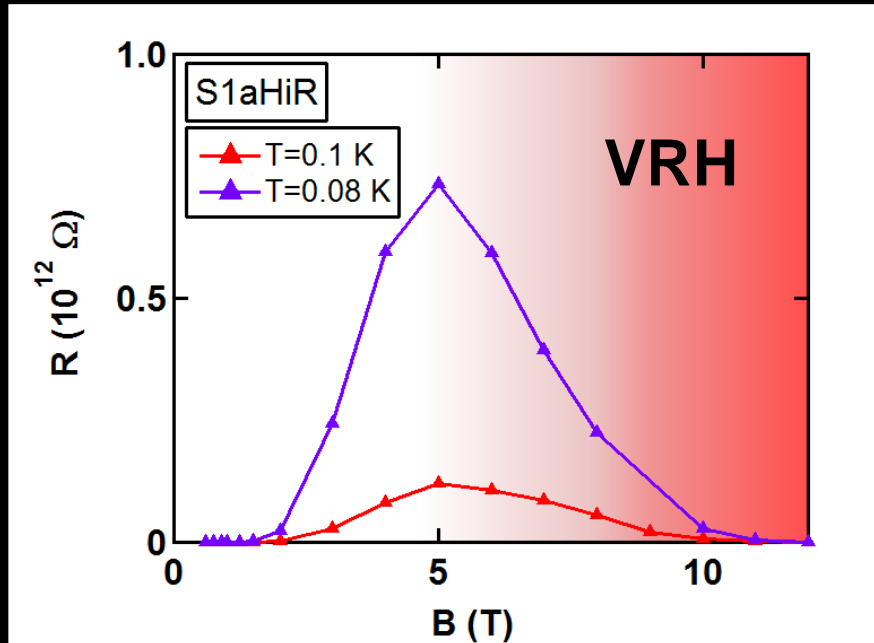


Arrhenius plot

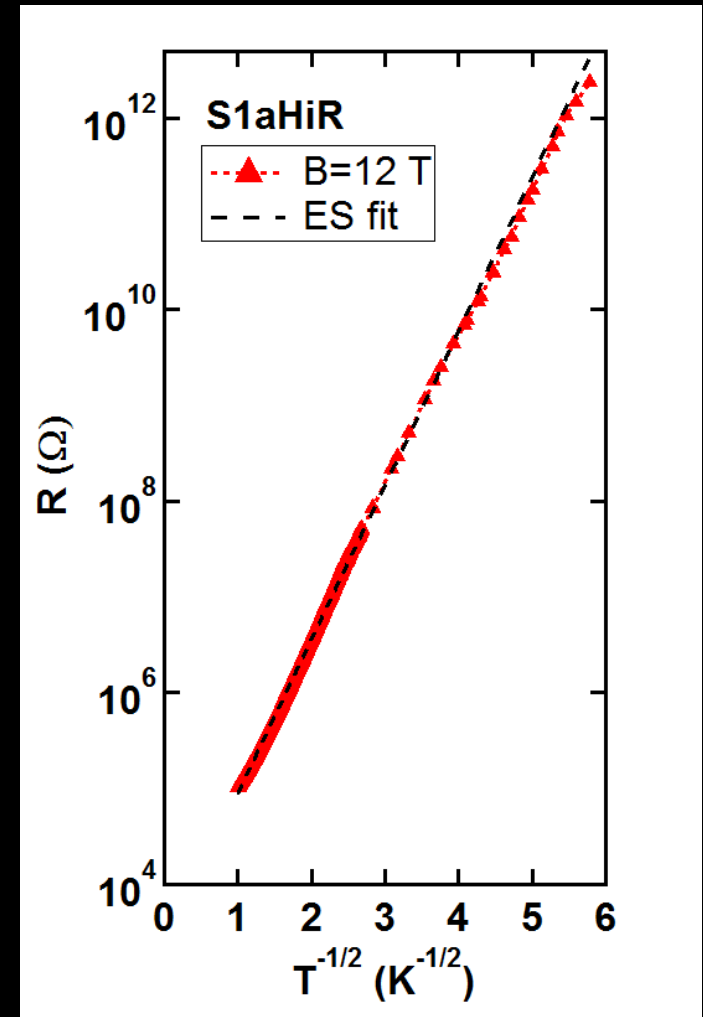
Activation



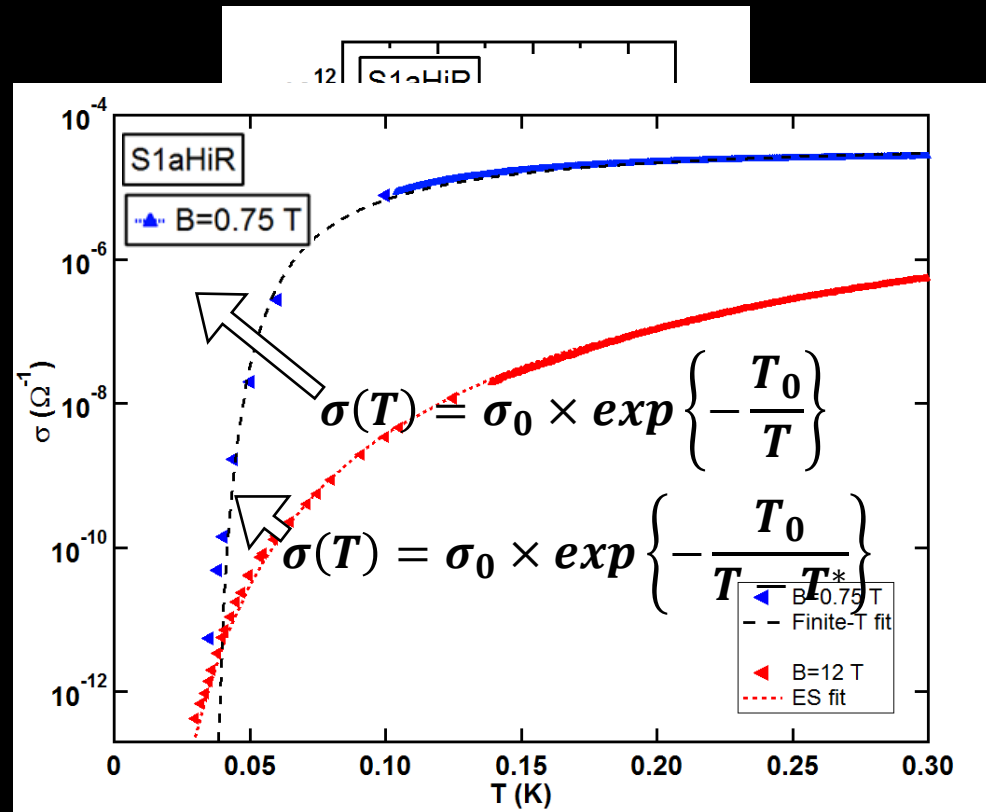
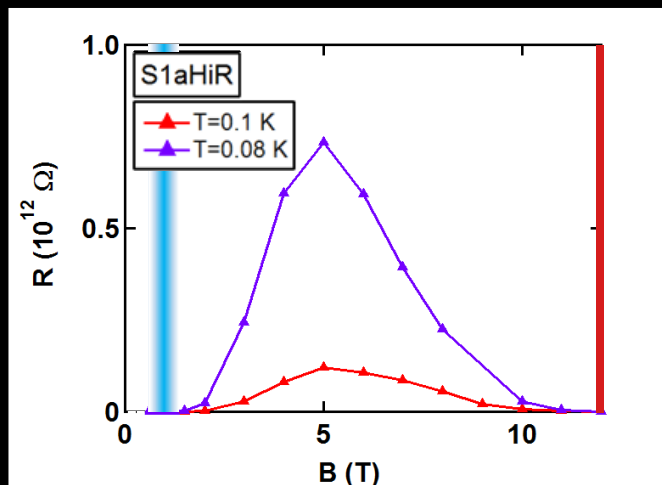
Efros-Shklovskii Hopping at high B



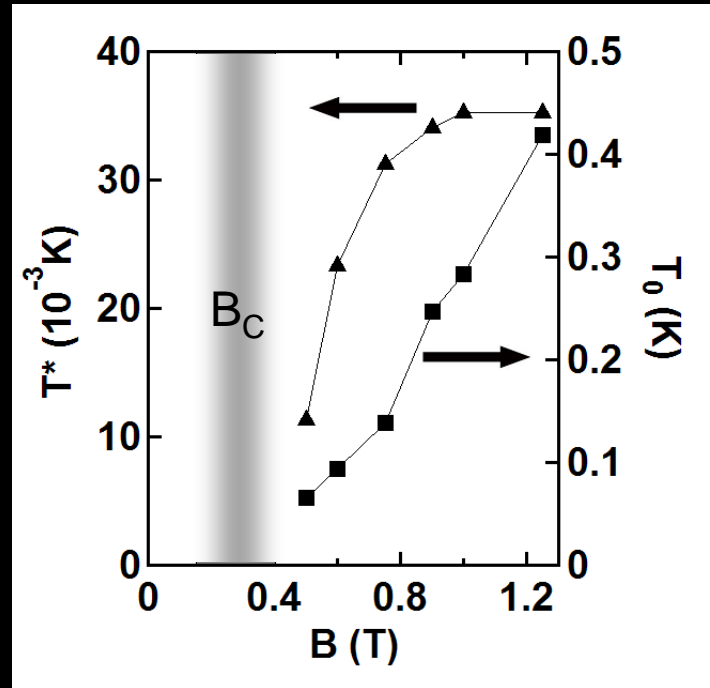
$$R(T) = R_{ES} \times \exp \left\{ \left(\frac{T_{ES}}{T} \right)^{1/2} \right\}$$



Resistivity ρ near B_c

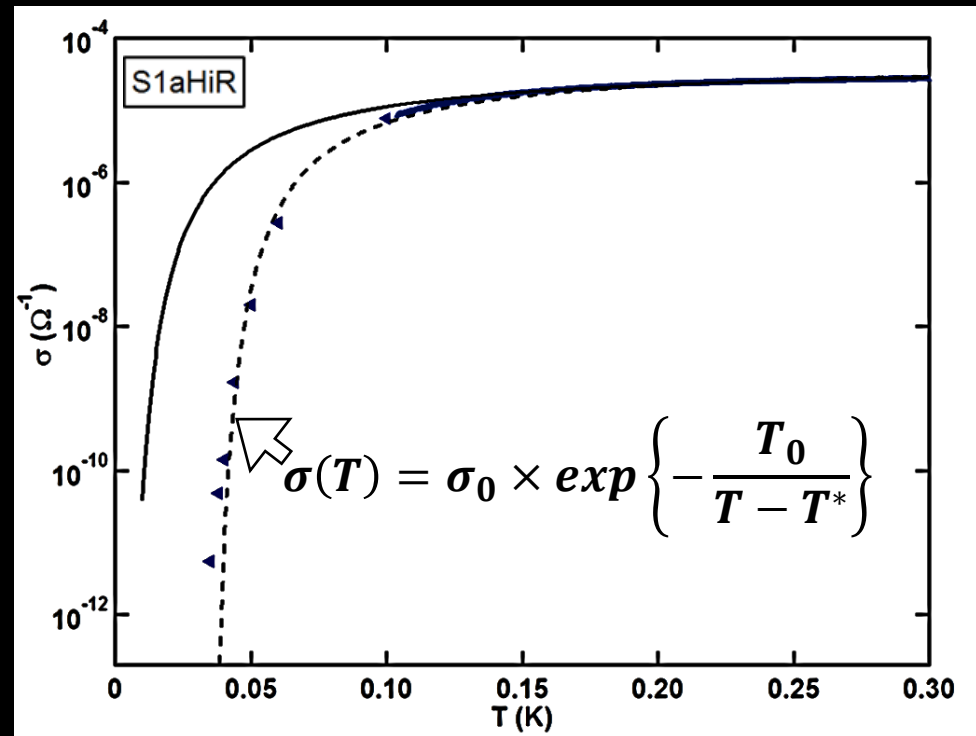


Fit Parameters



$$\sigma(T) = \sigma_0 \times \exp\left\{-\frac{T_0}{T - T^*}\right\}$$

Many-body localization ?



Thank you.